

FIG. 1A

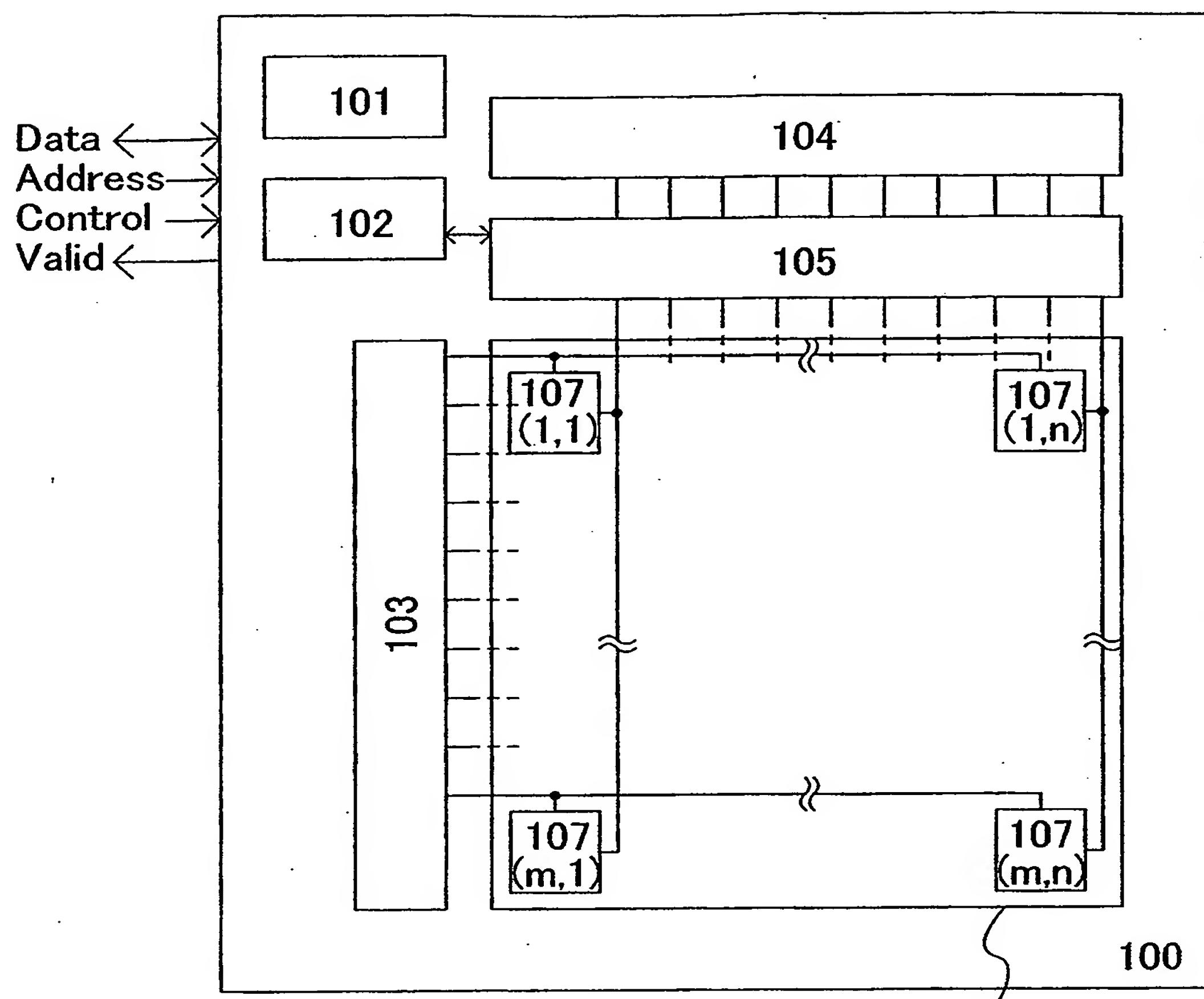


FIG. 1B

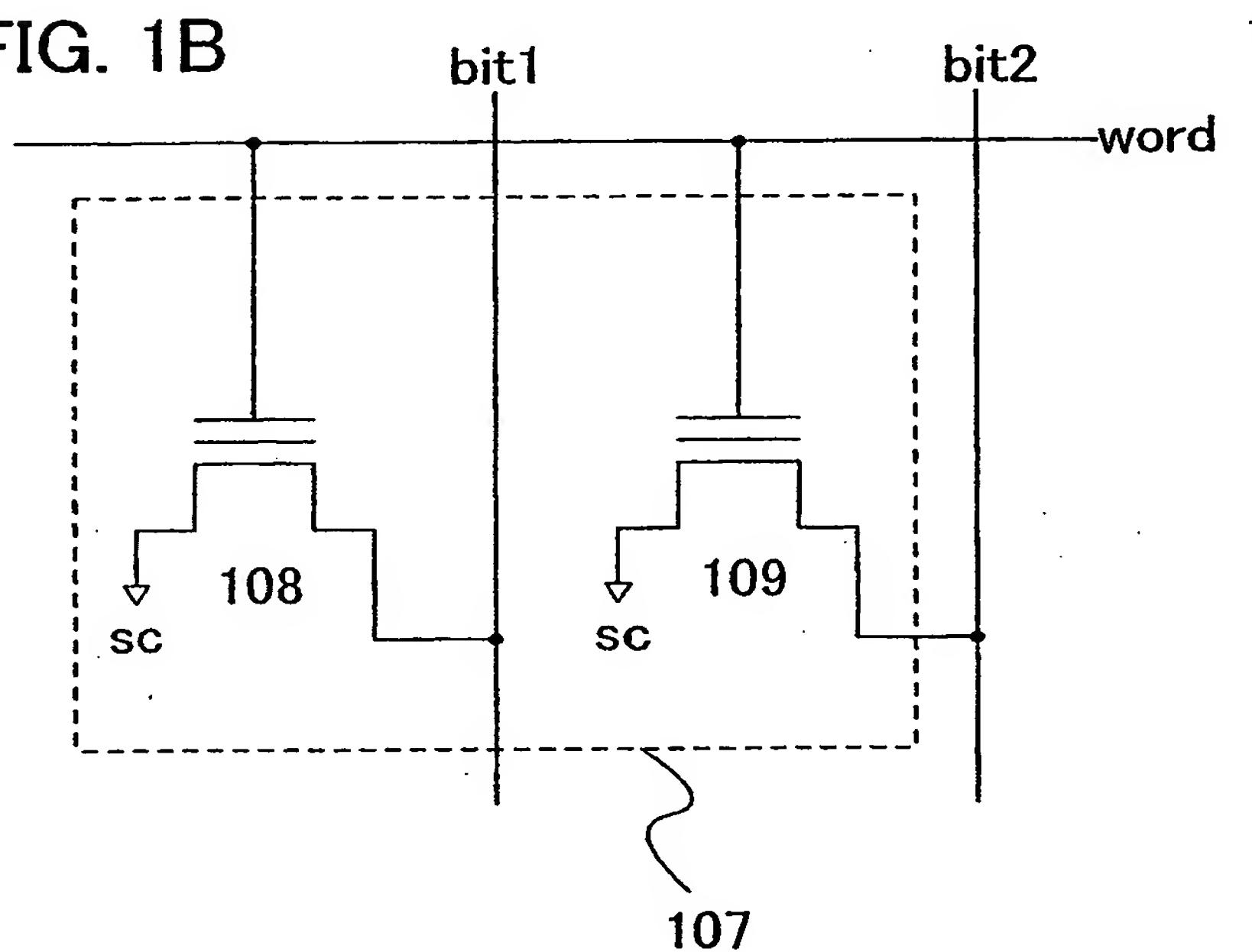


FIG. 2A

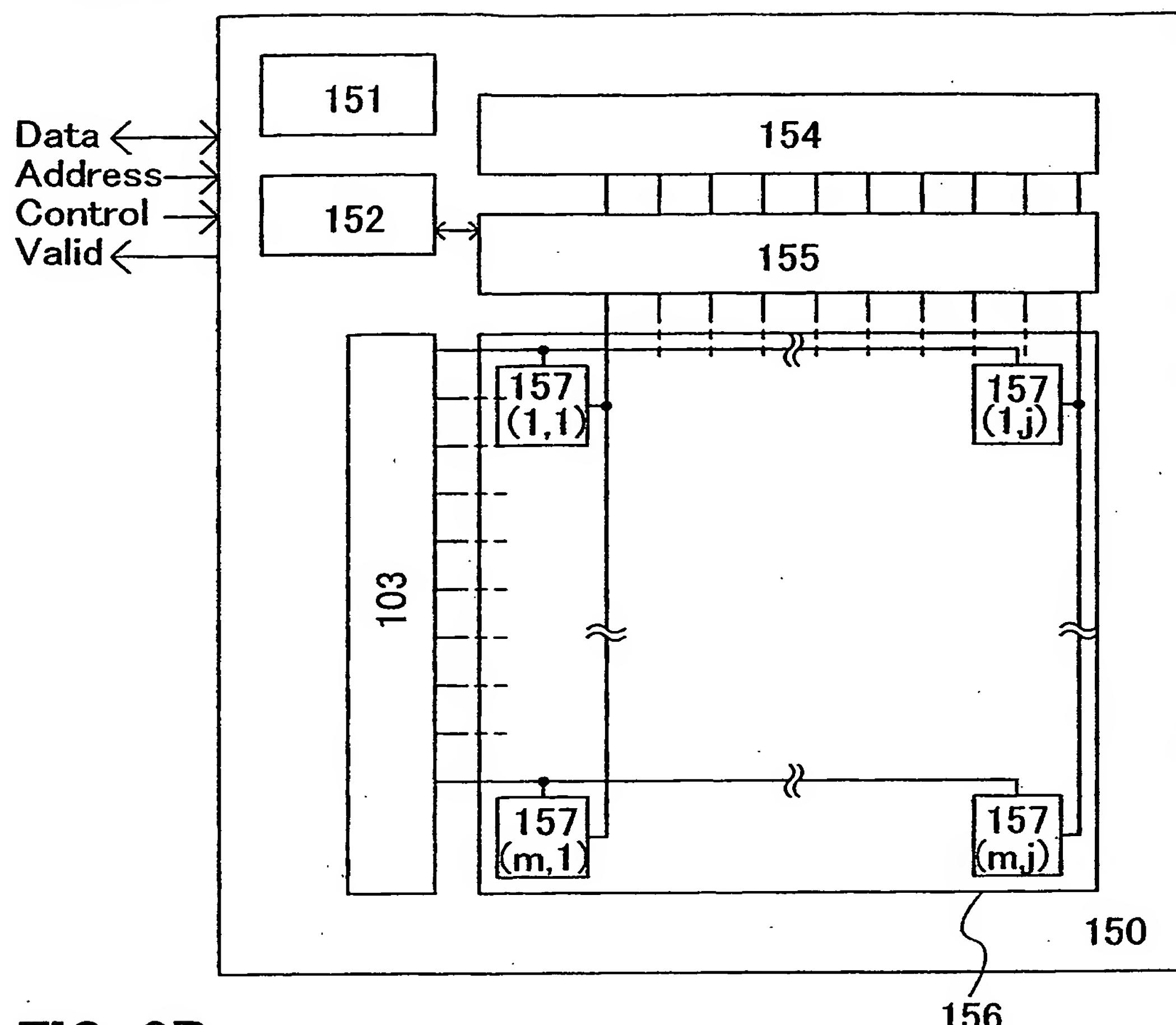


FIG. 2B

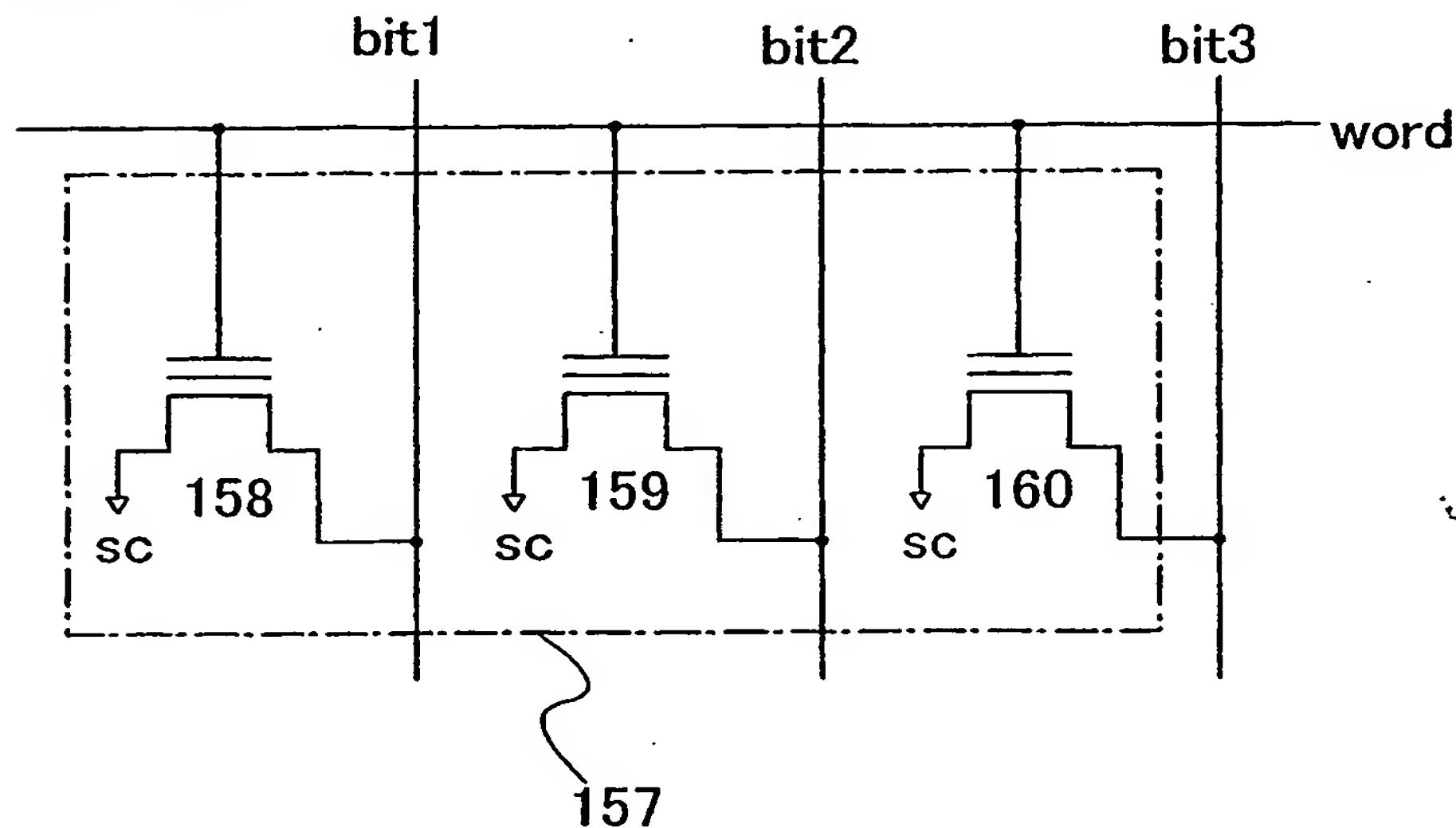


FIG. 3

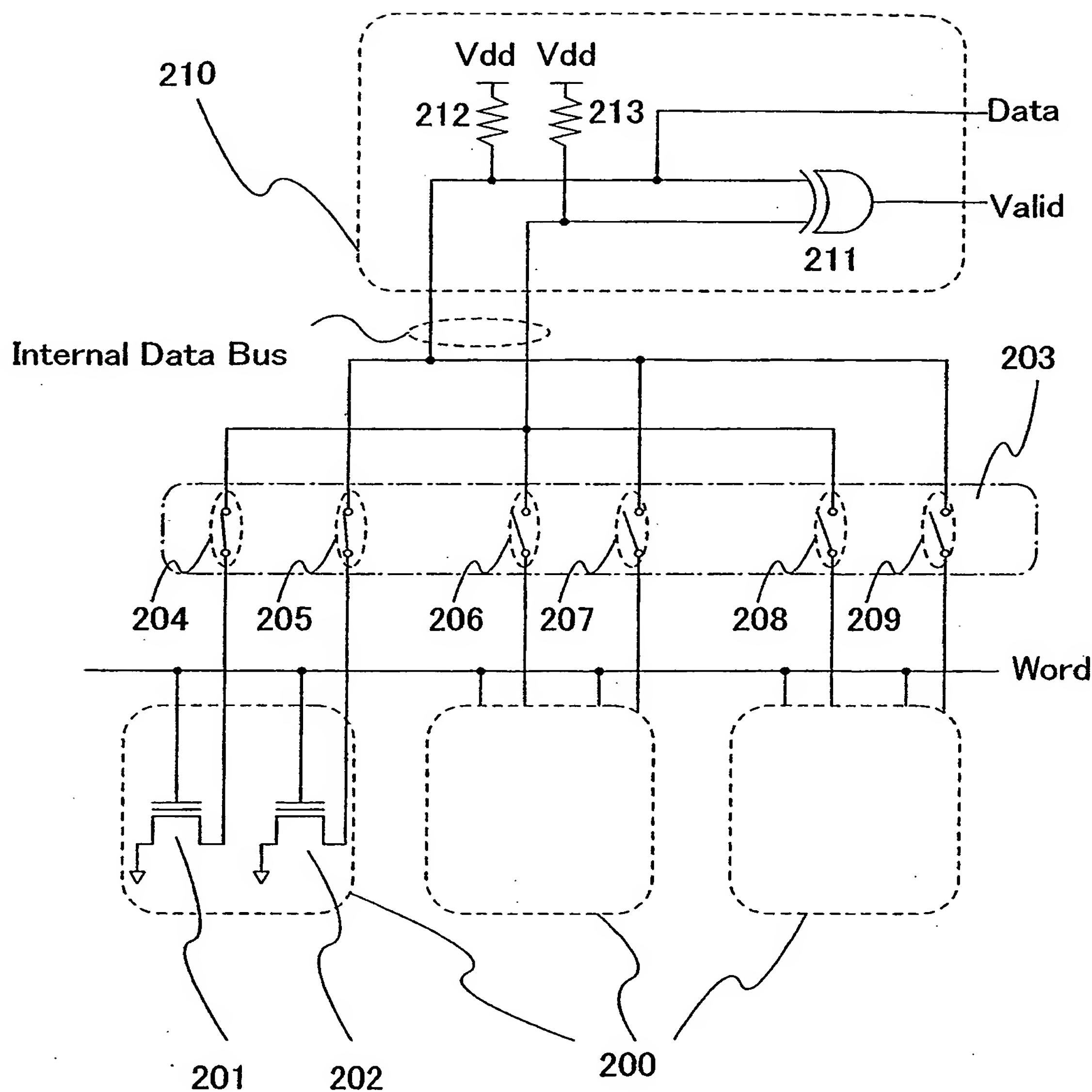
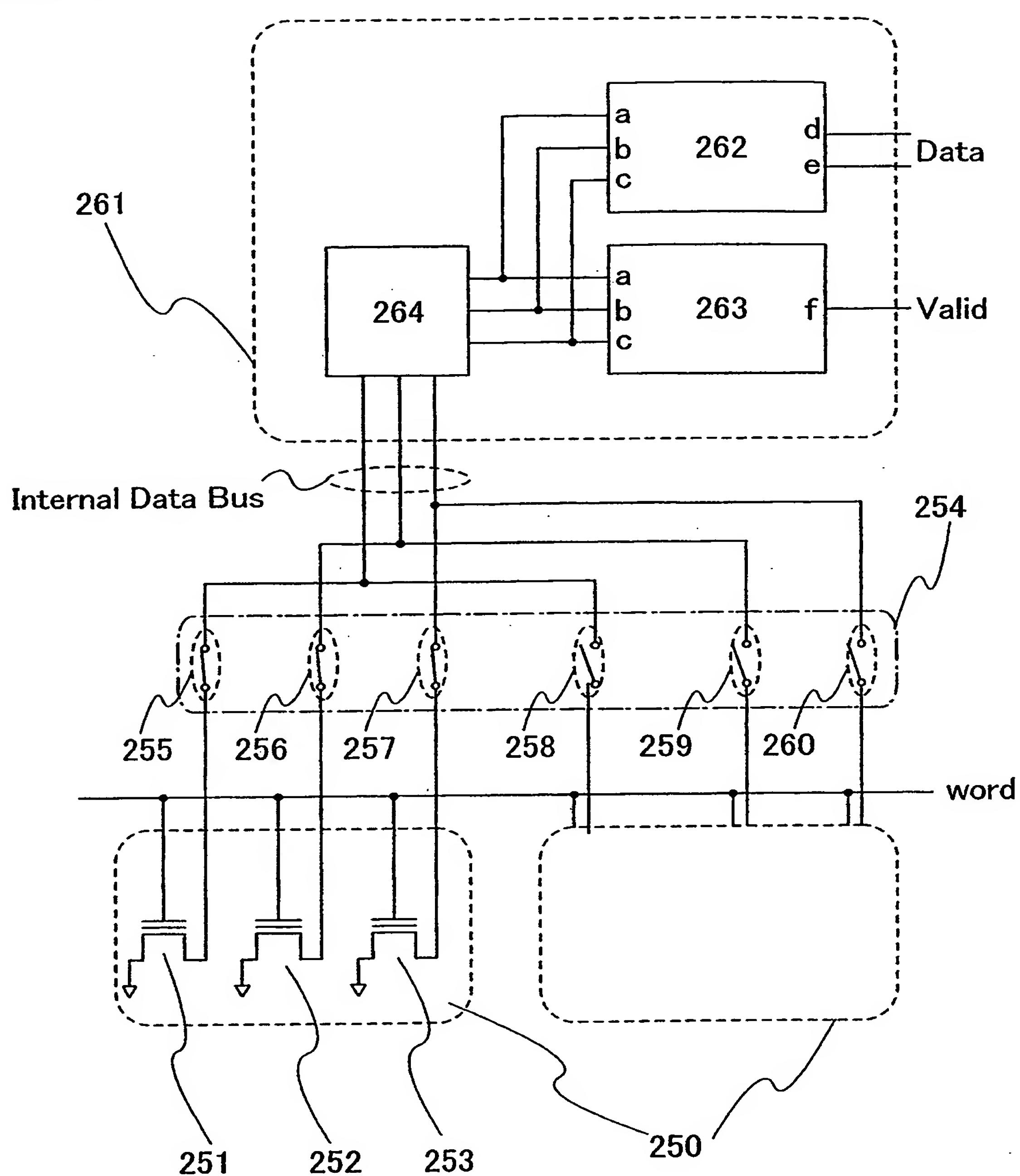


FIG. 4



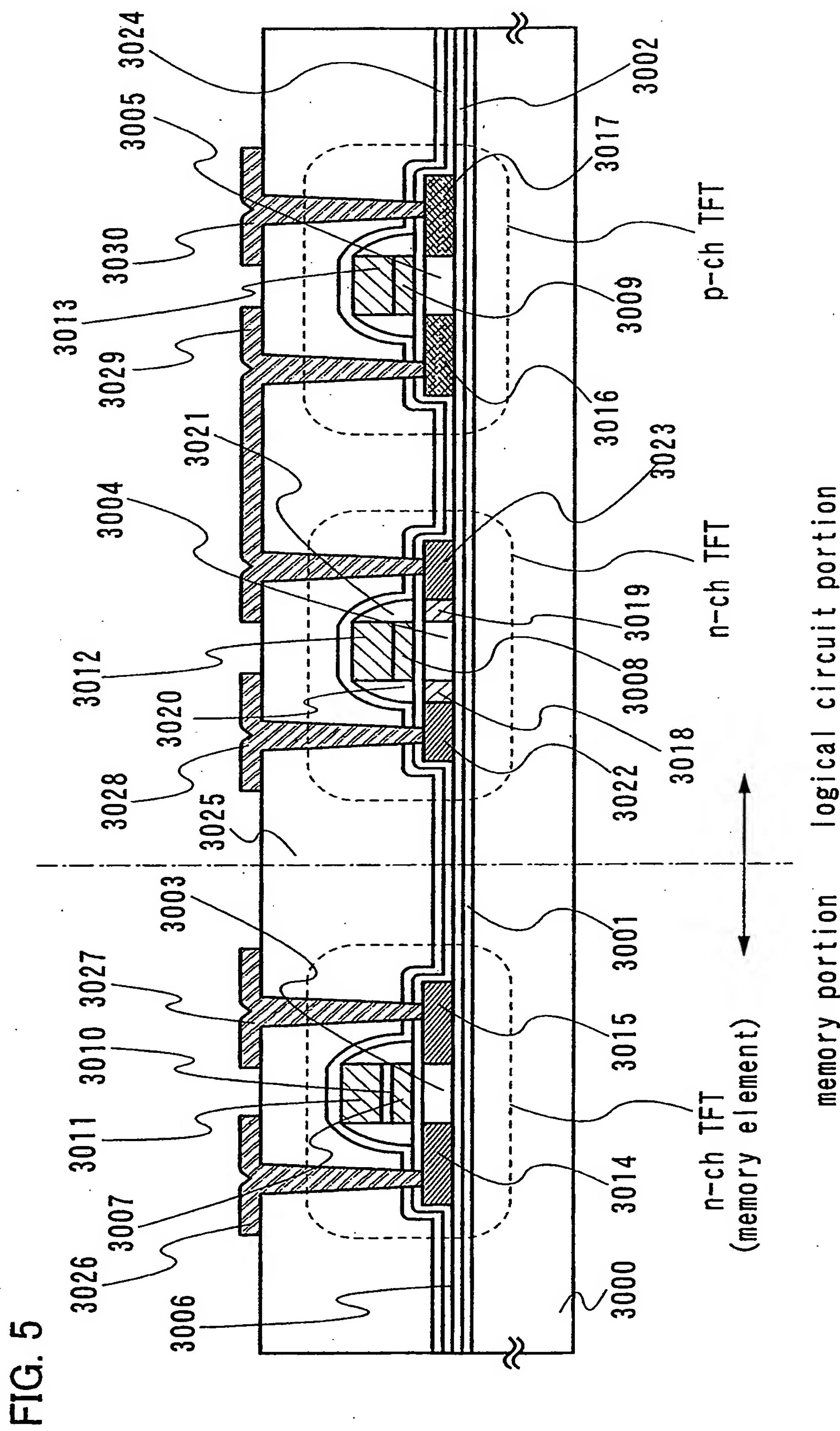
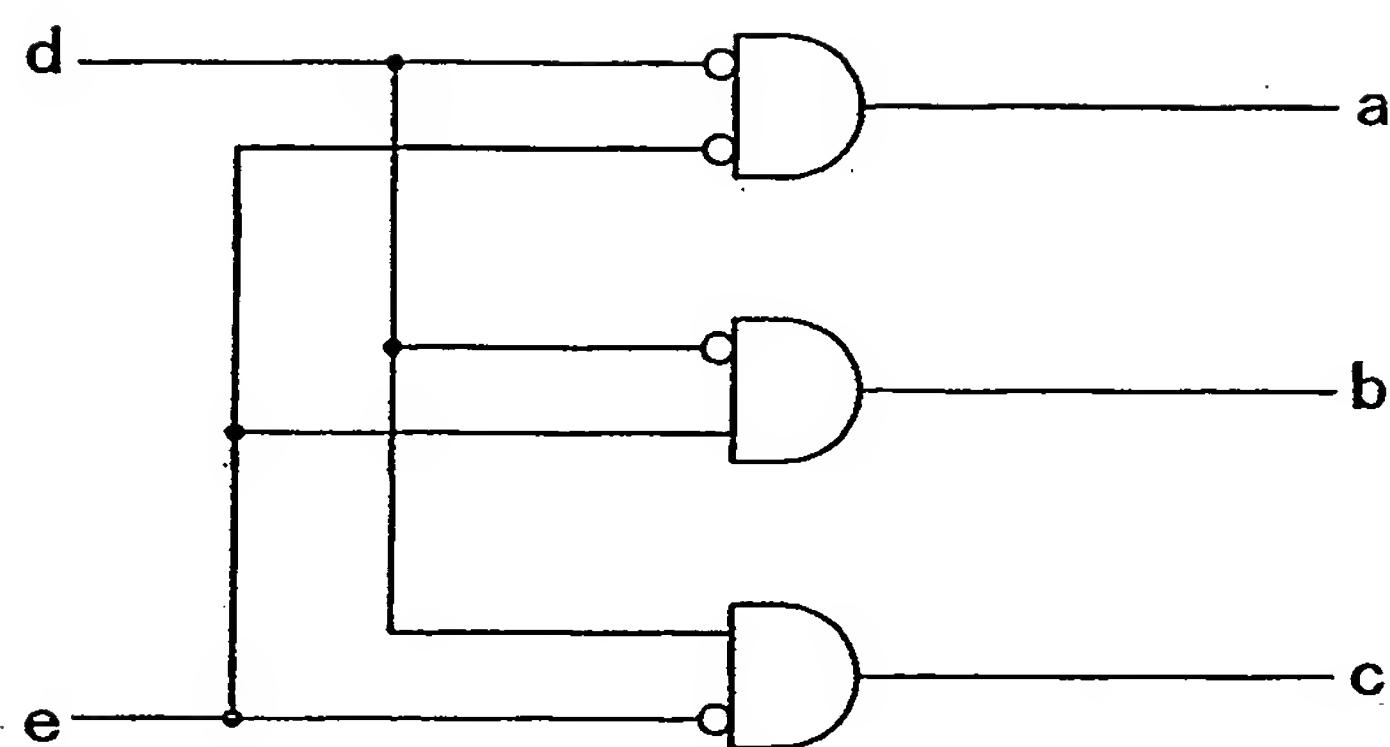


FIG. 5

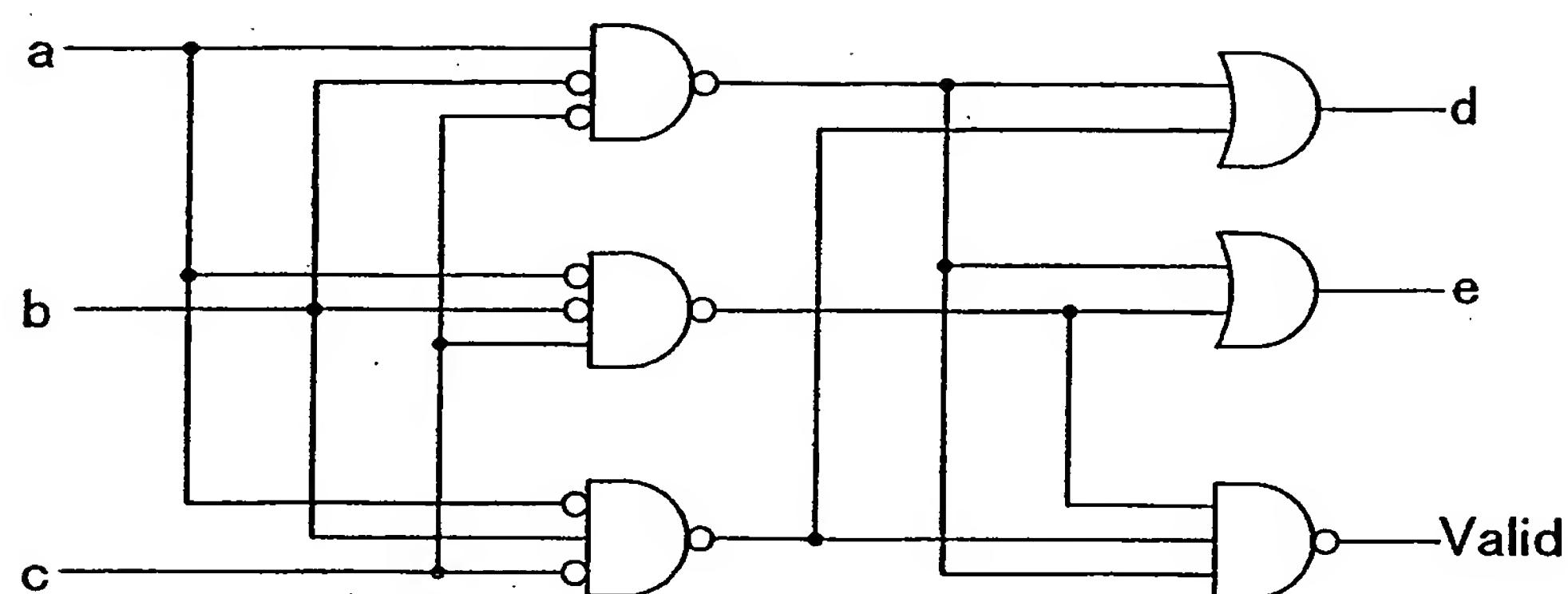
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FIG. 6



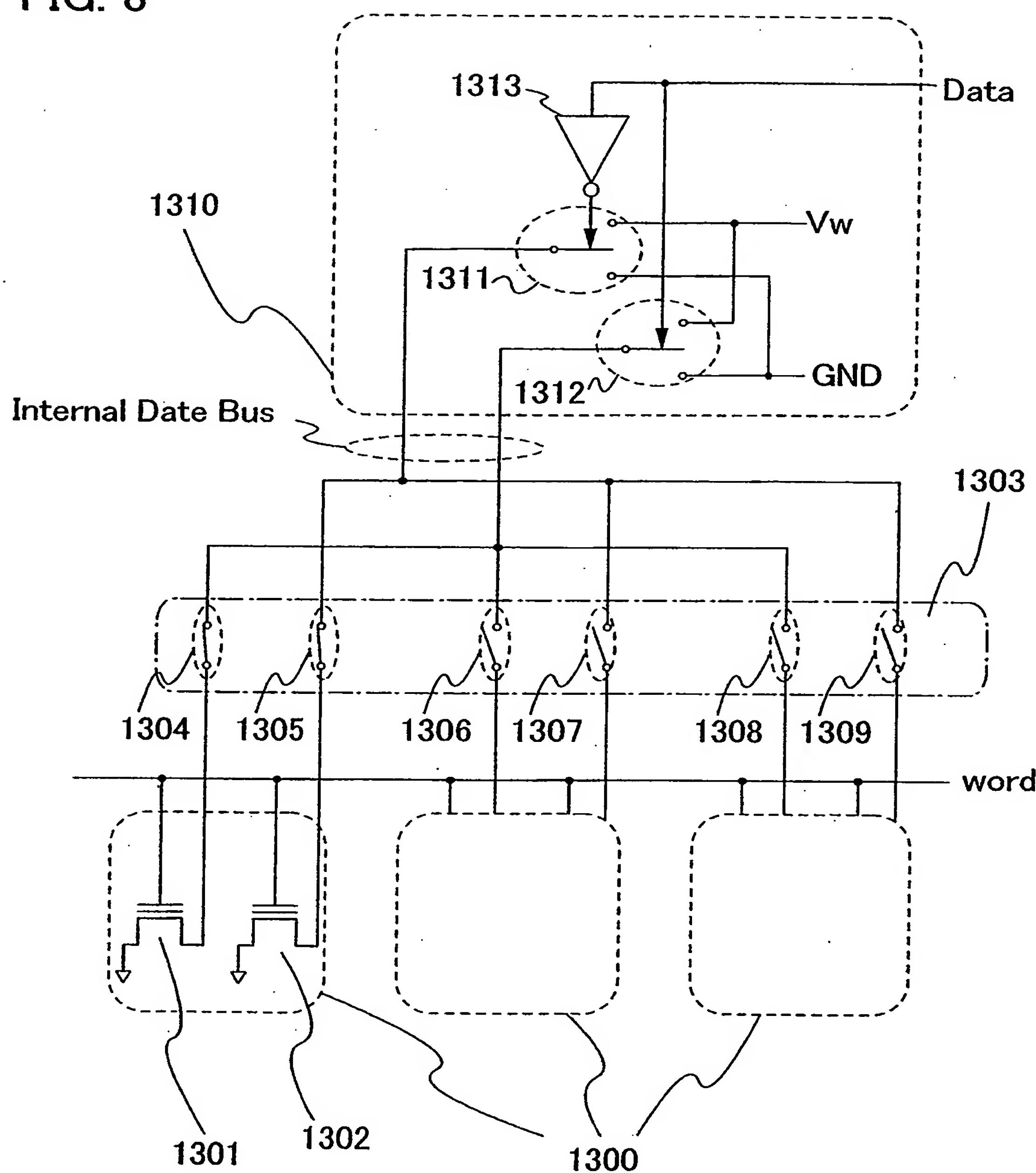
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FIG. 7



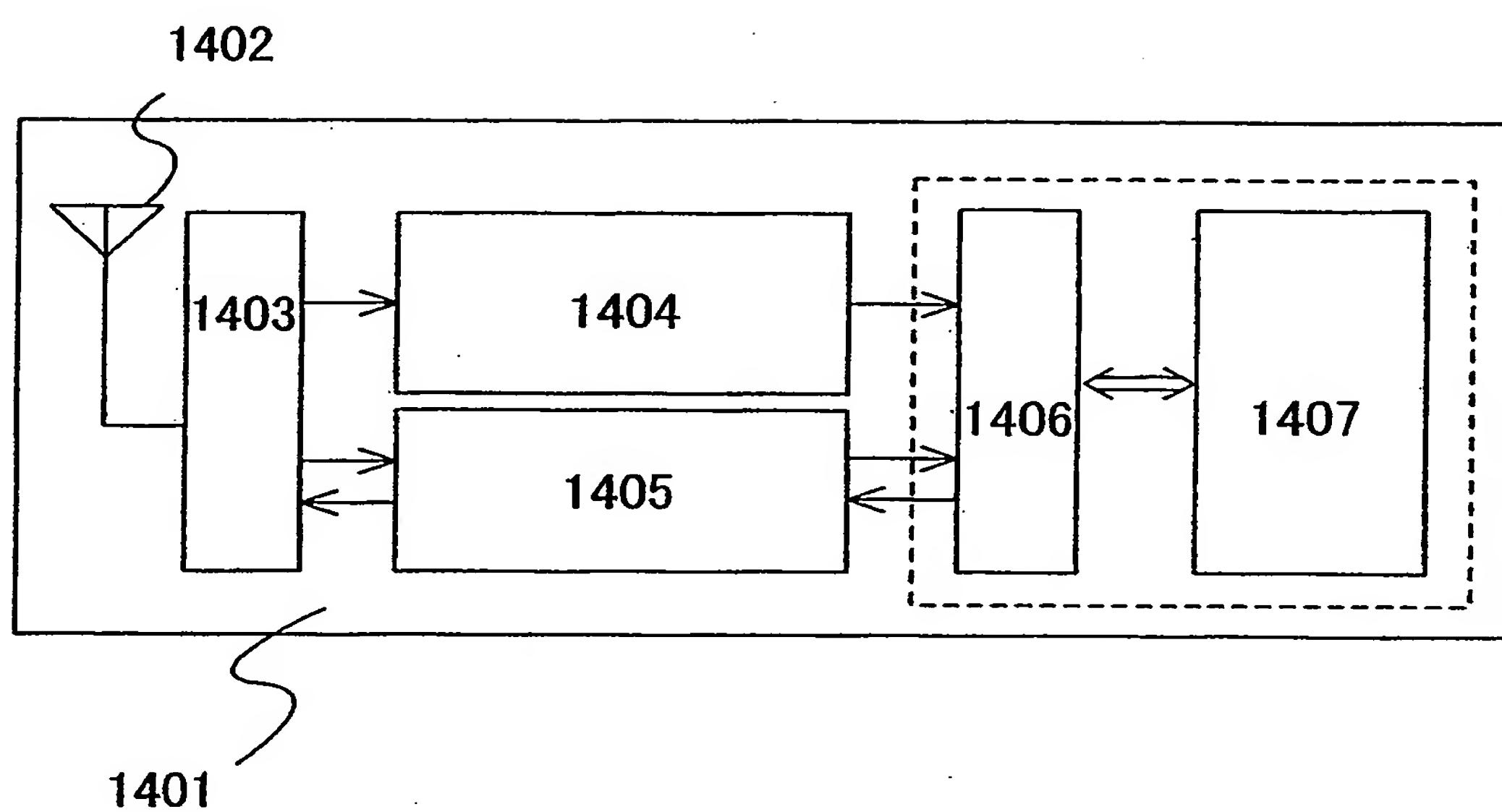
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FIG. 8



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FIG. 9



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FIG. 10A

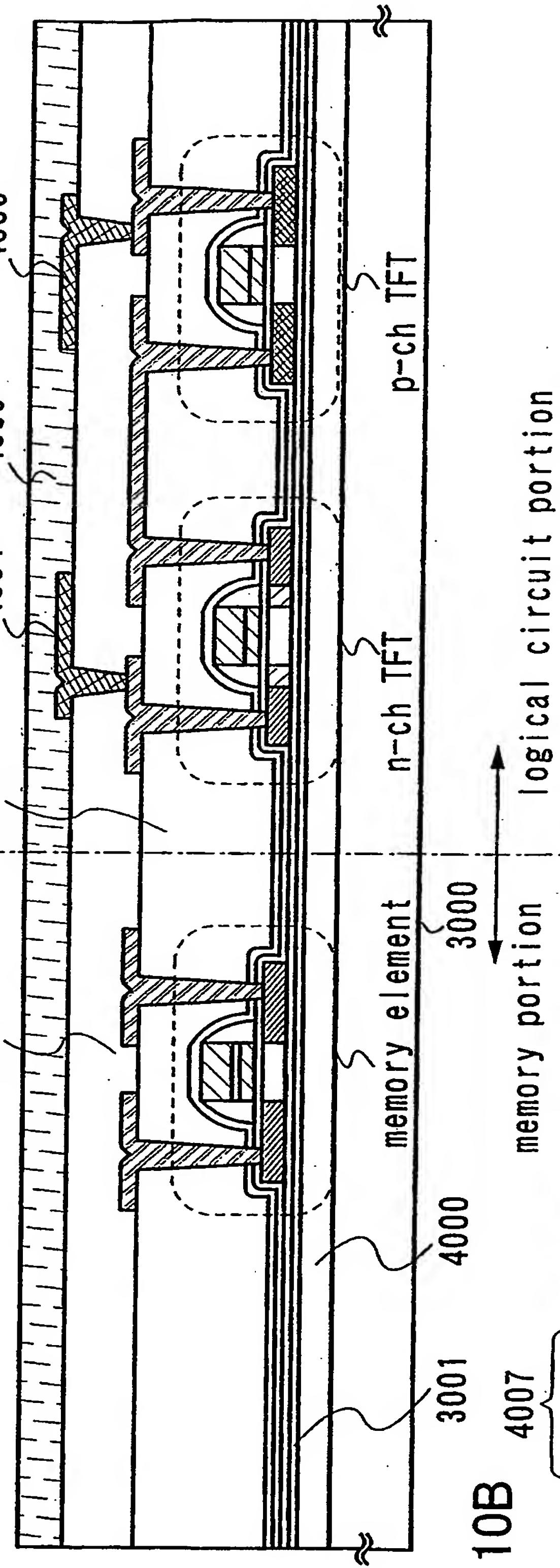
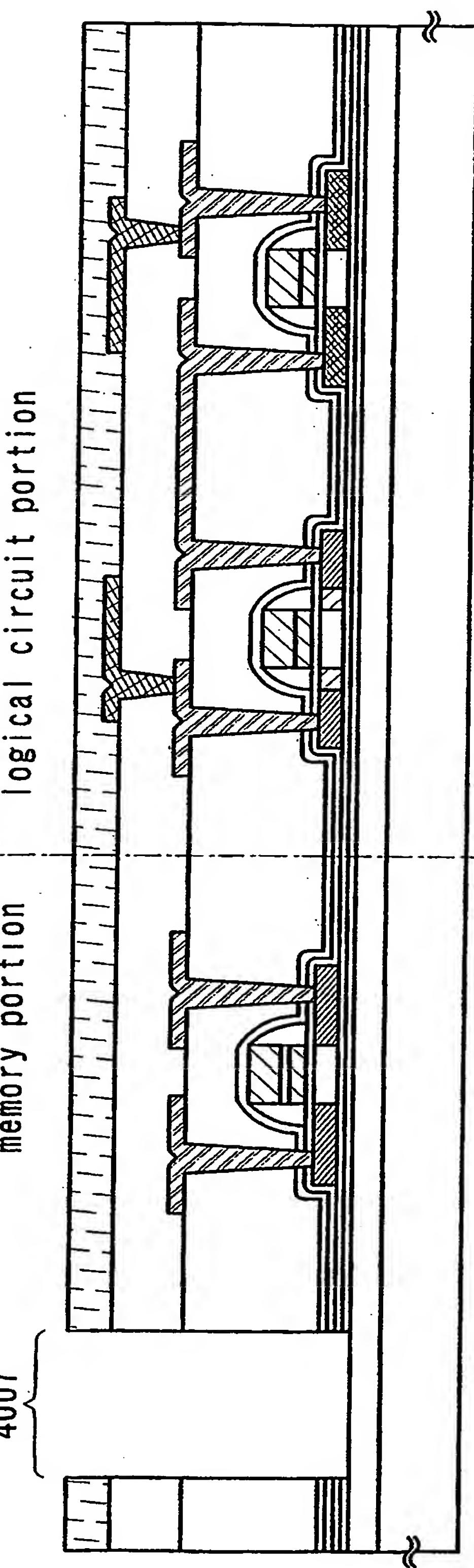
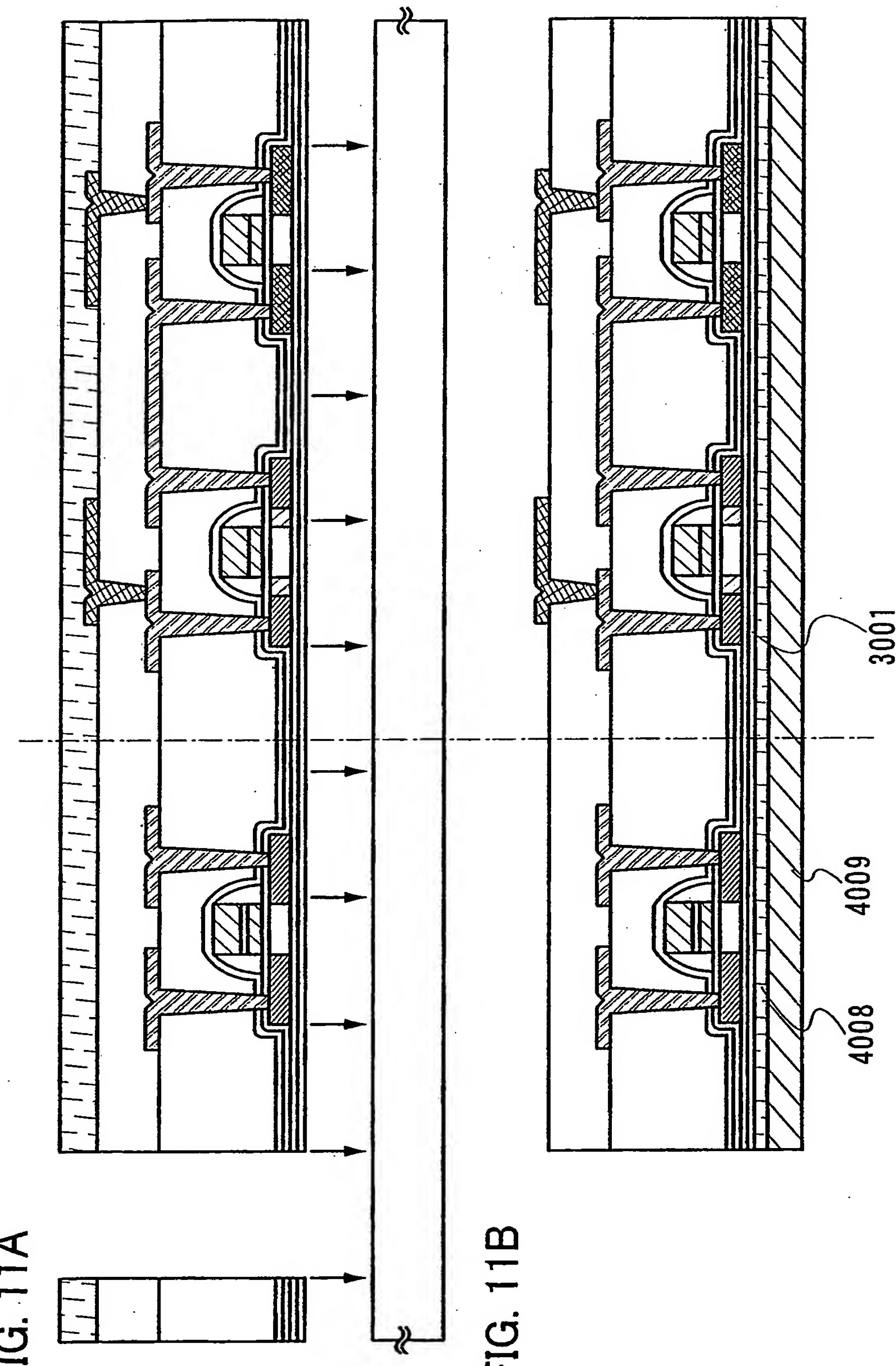


FIG. 10B





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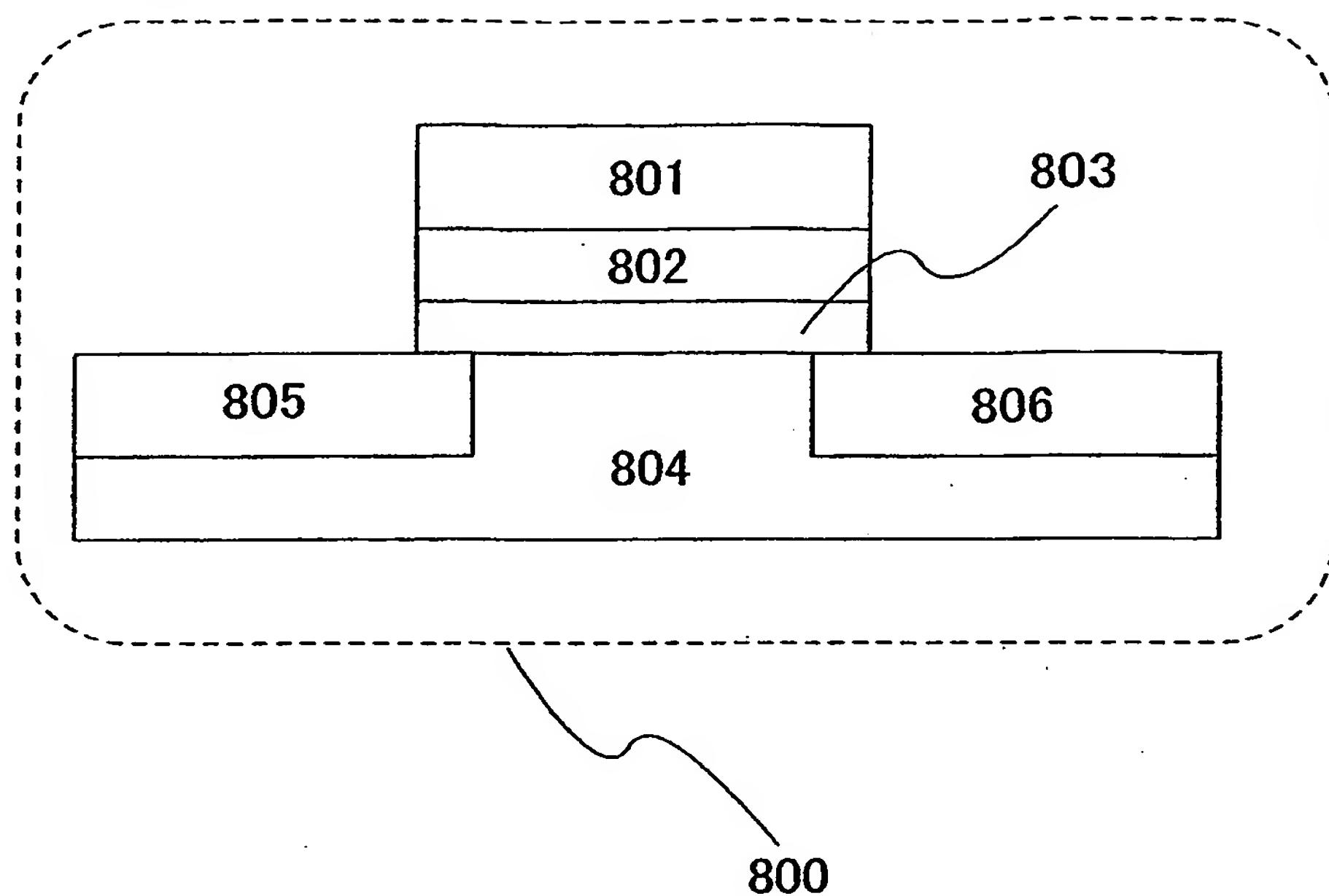
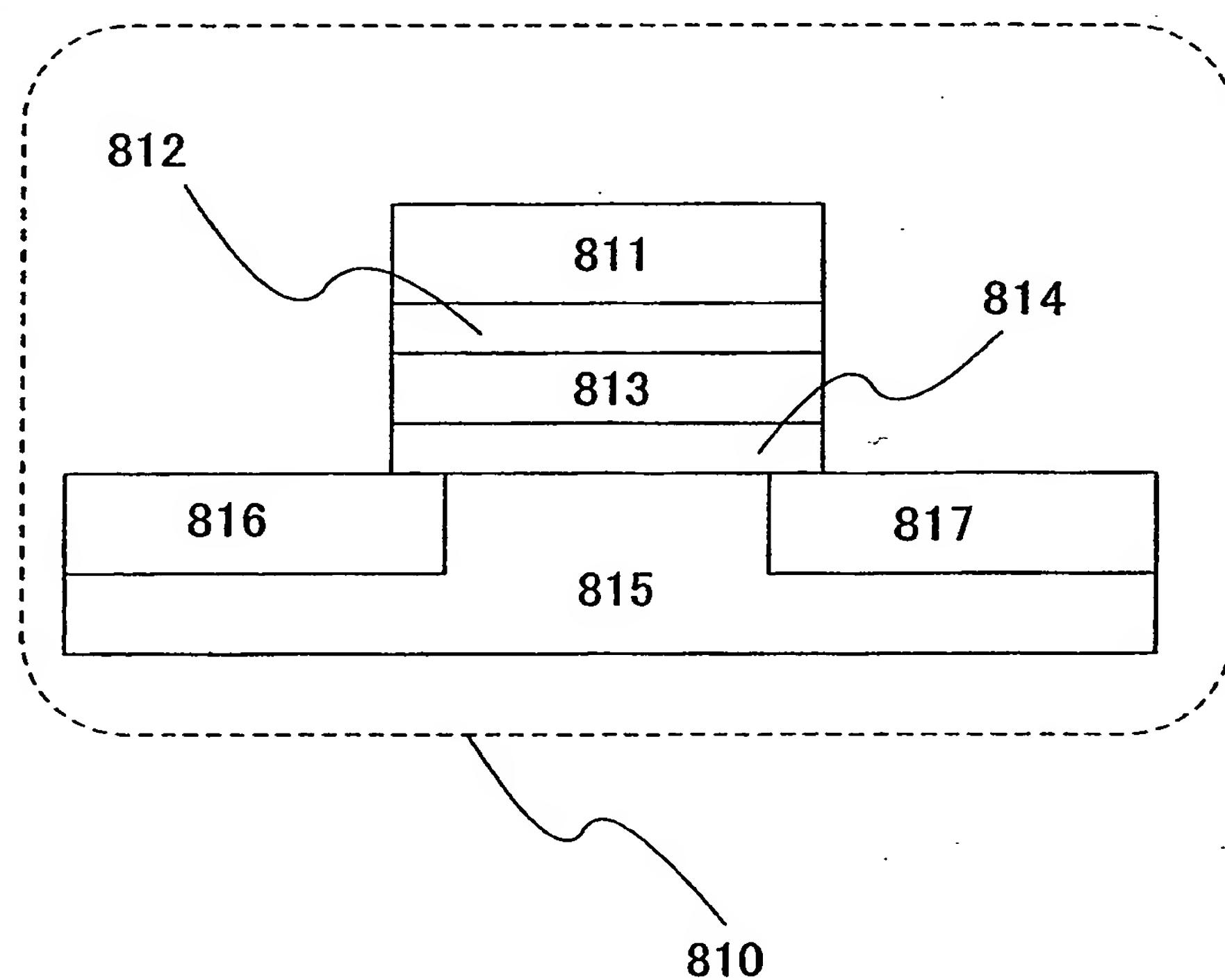
FIG. 12A**FIG. 12B**

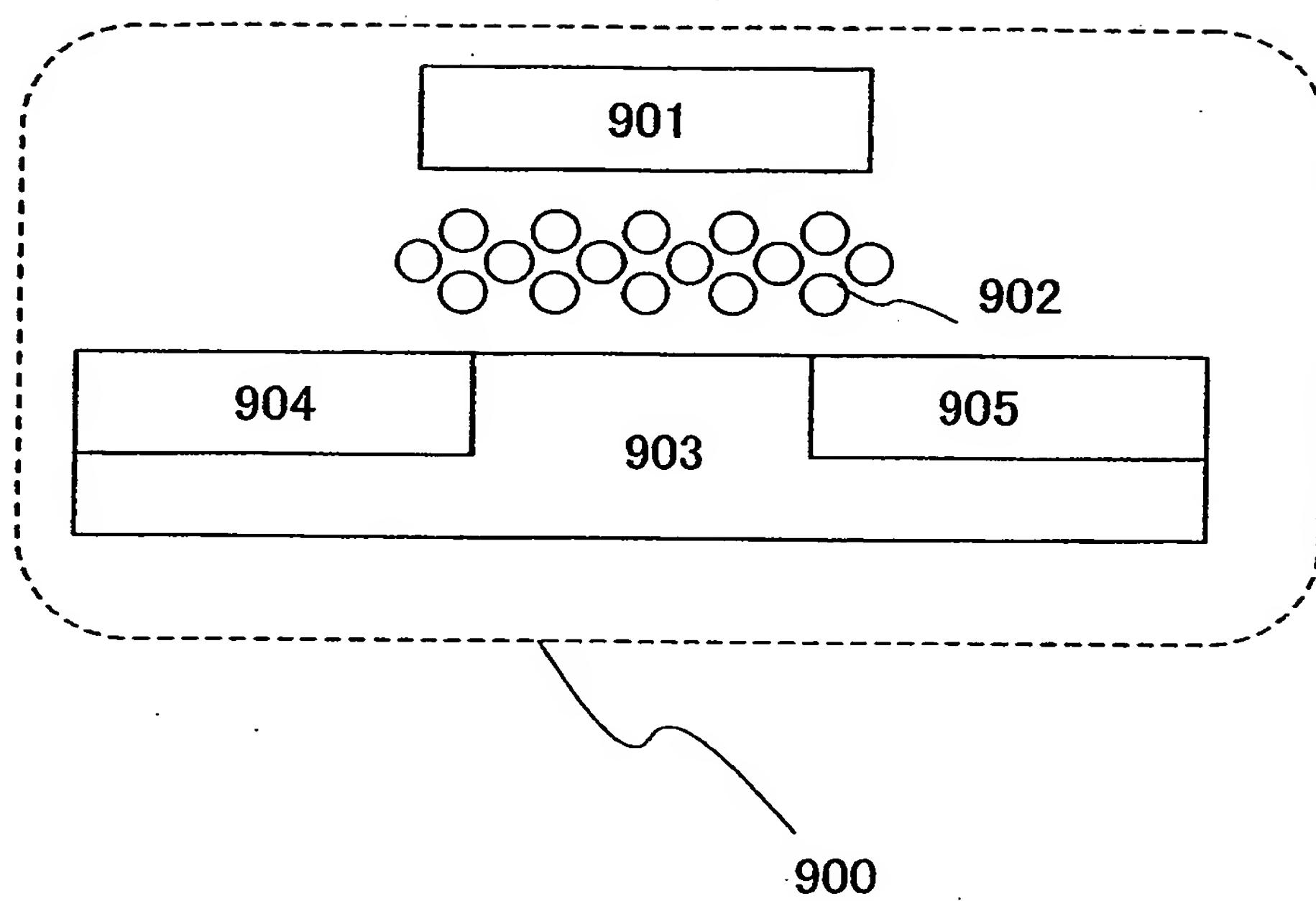
FIG. 13

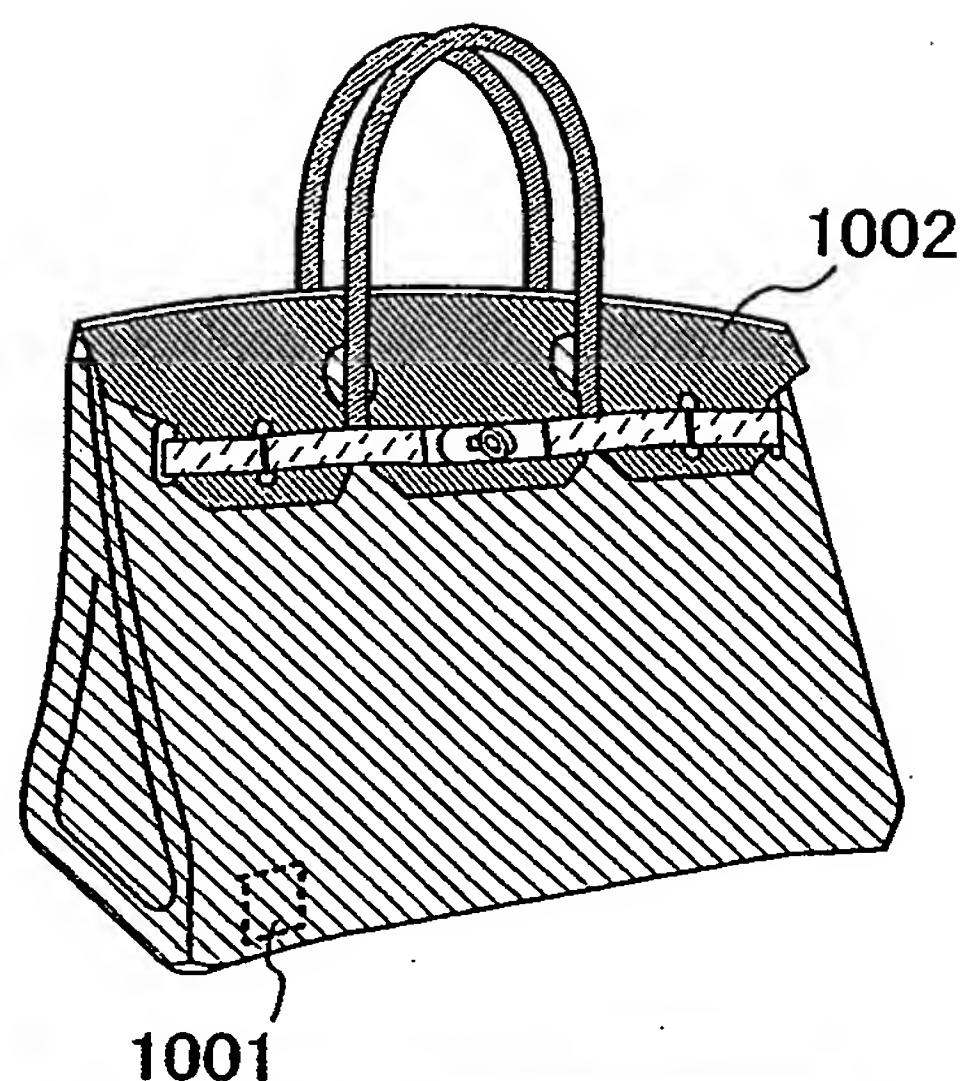
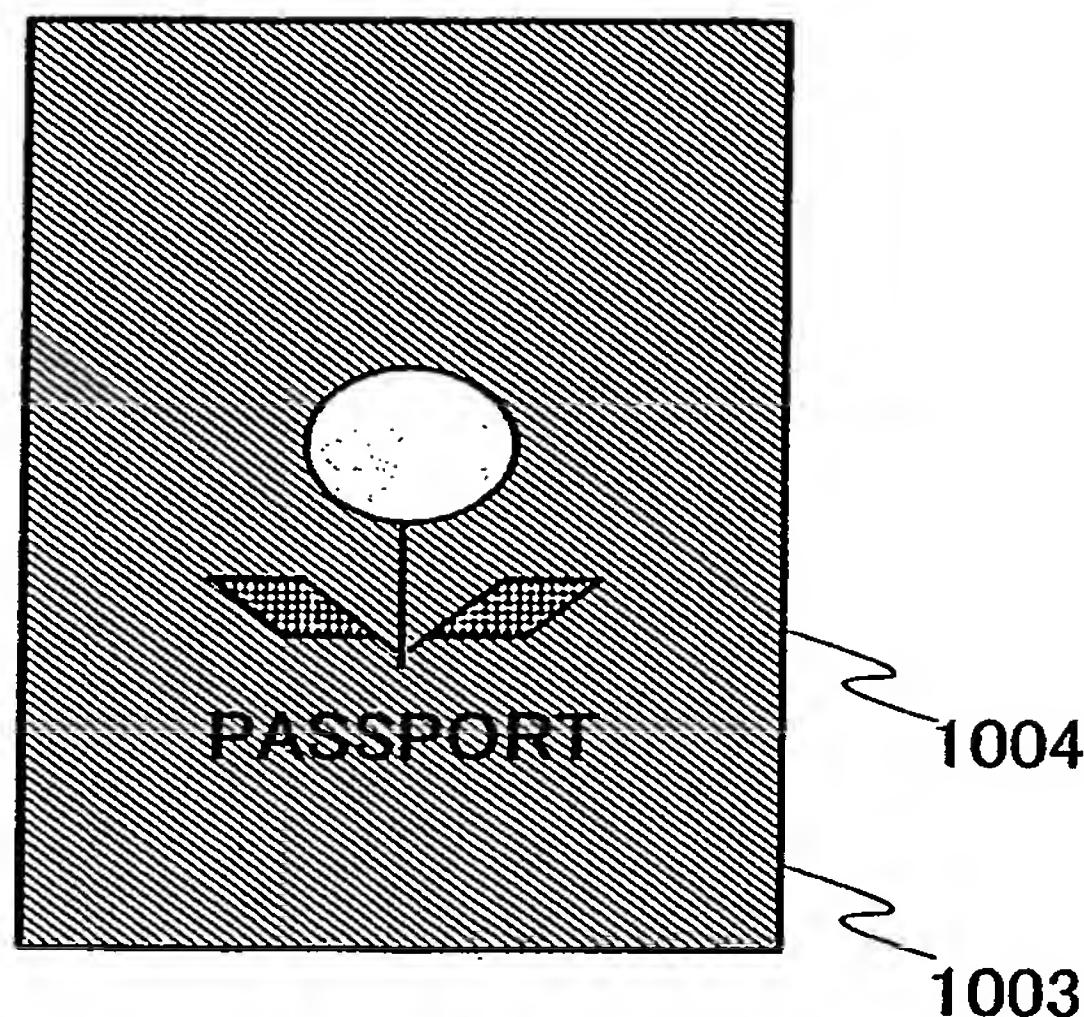
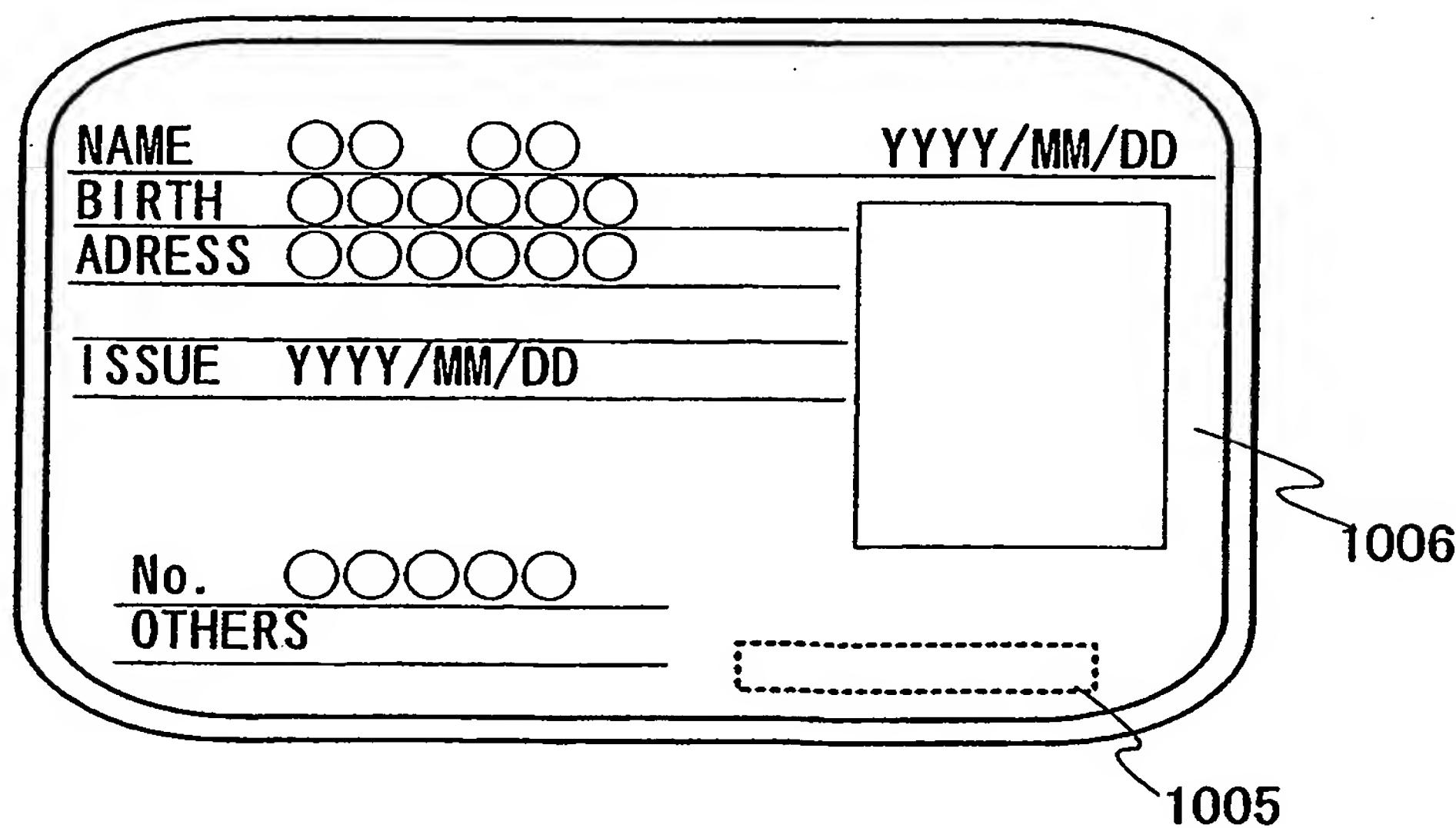
FIG. 14A**FIG. 14B****FIG. 14C**

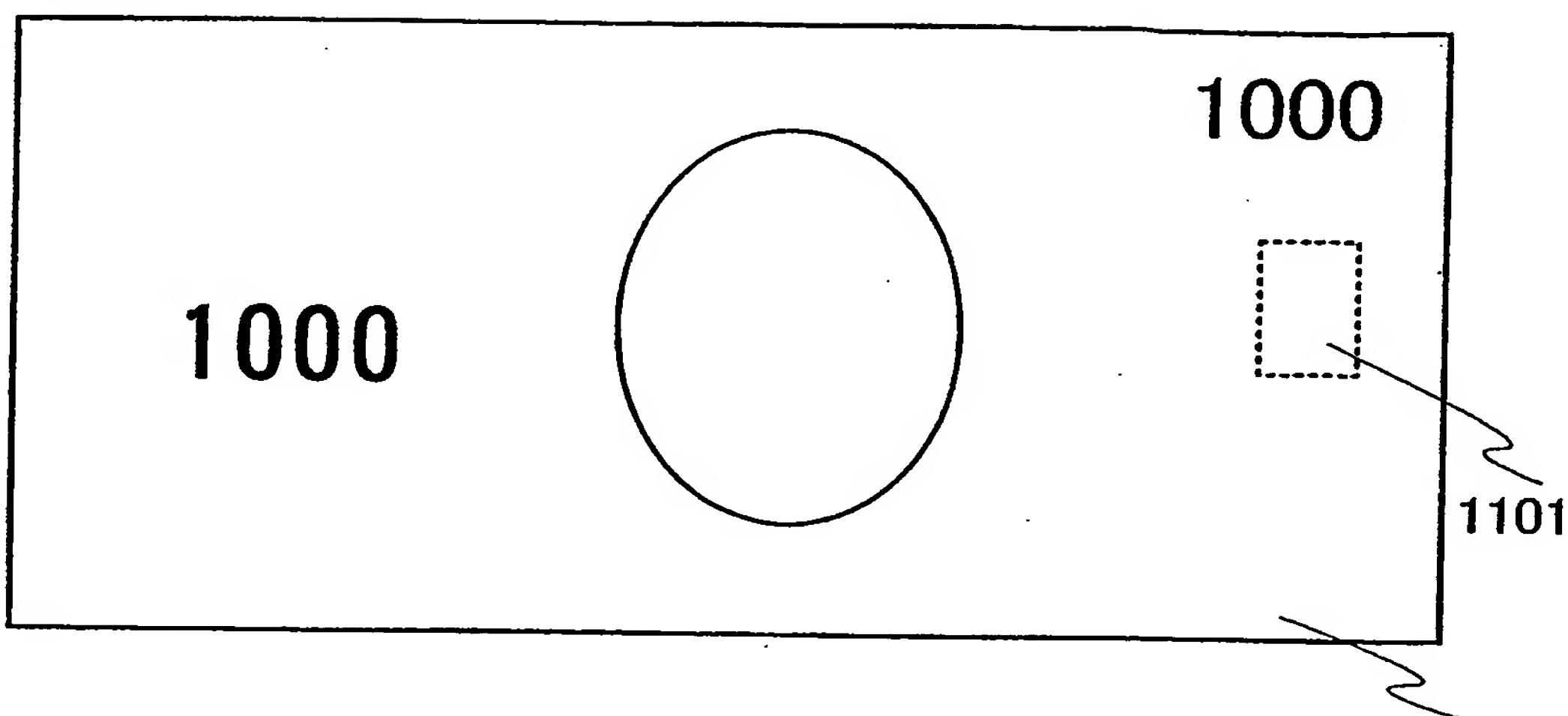
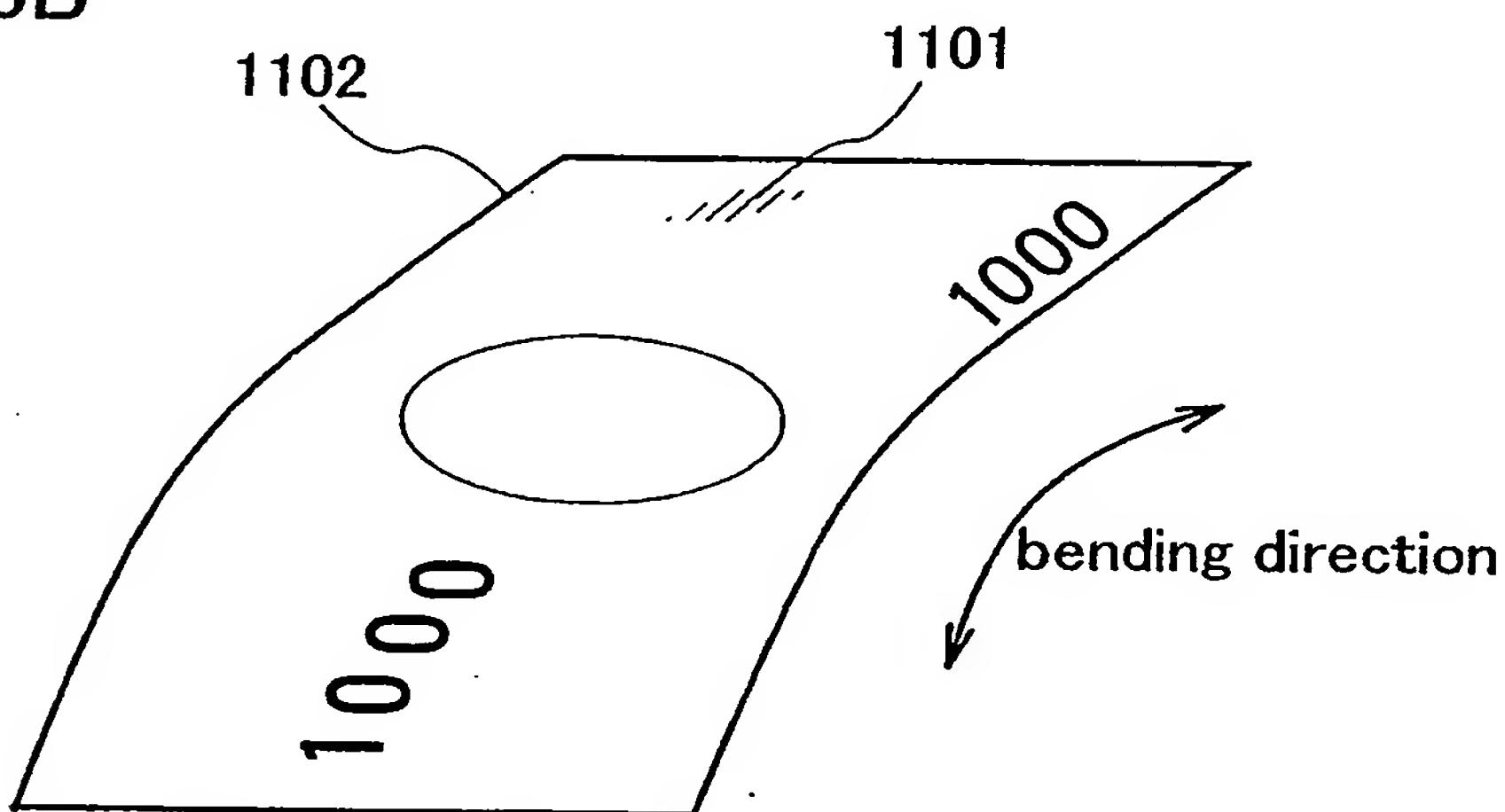
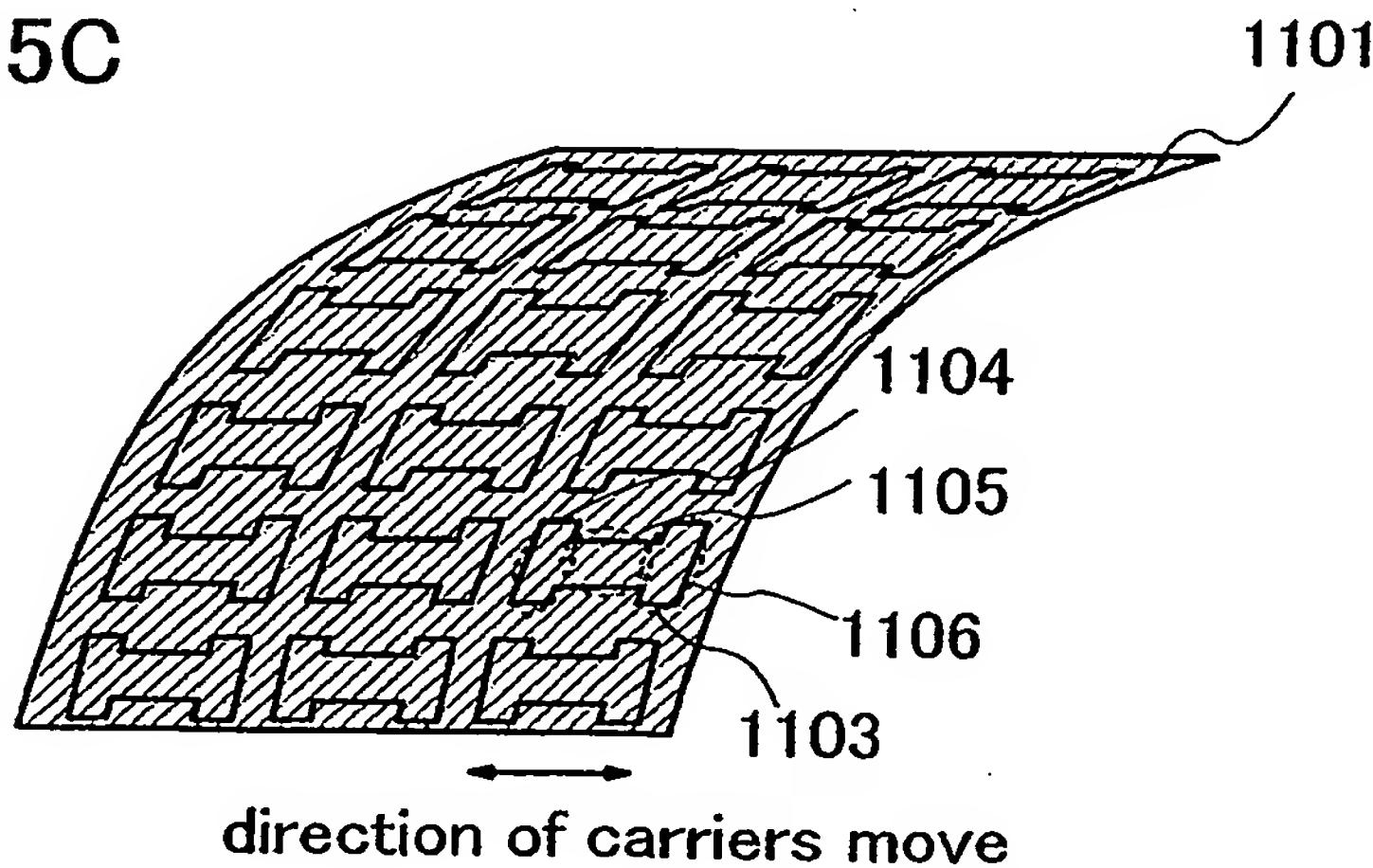
FIG. 15A**FIG. 15B****FIG. 15C**

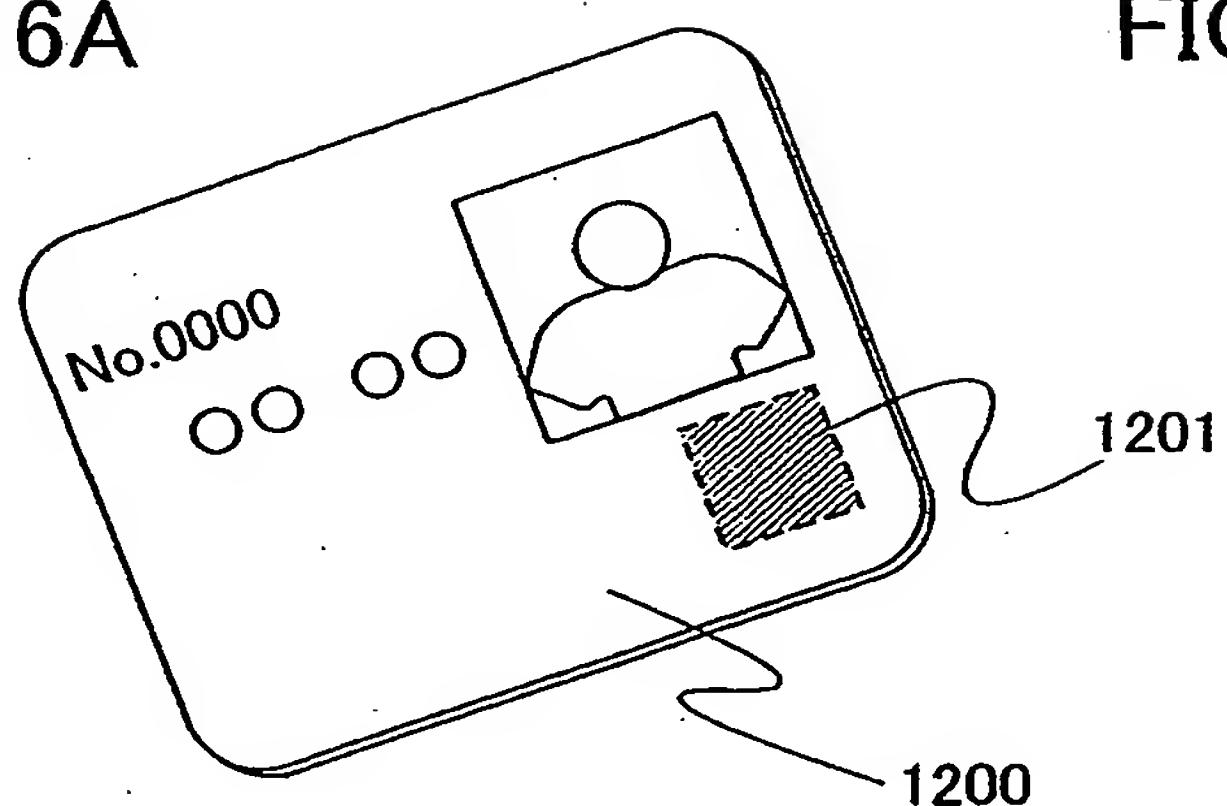
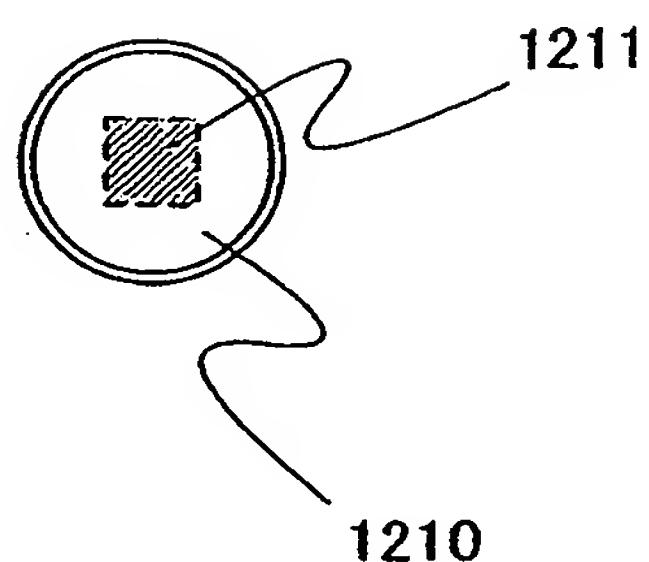
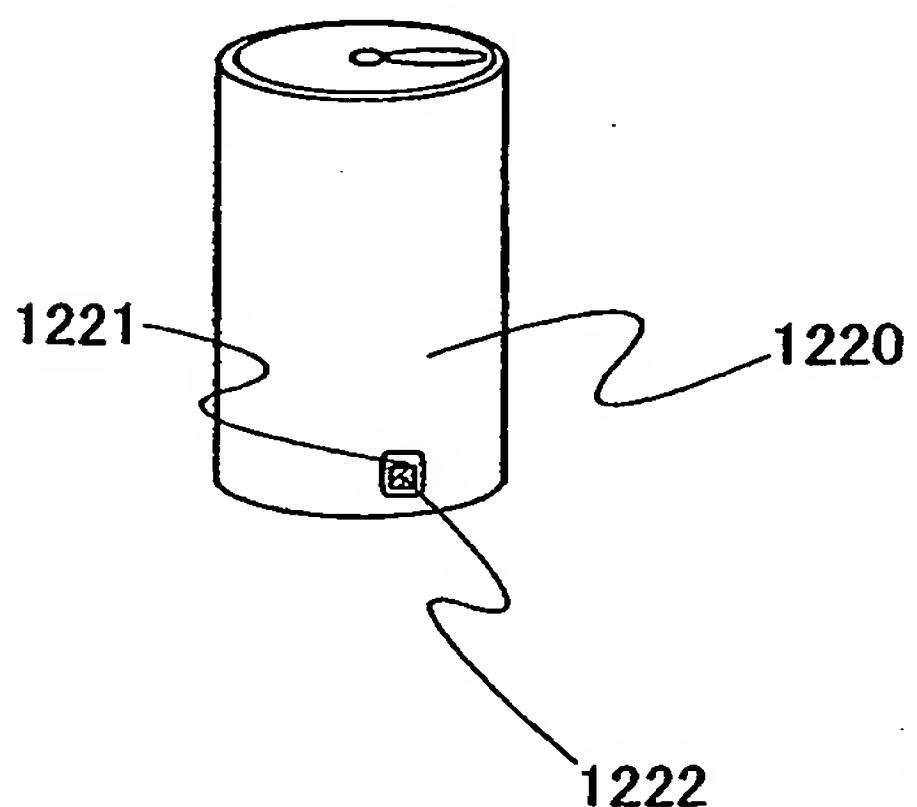
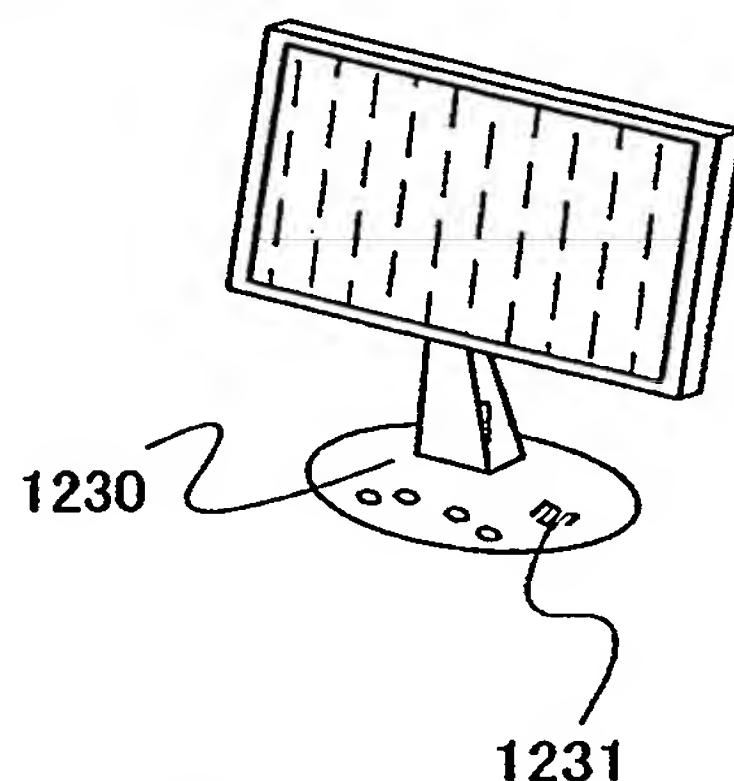
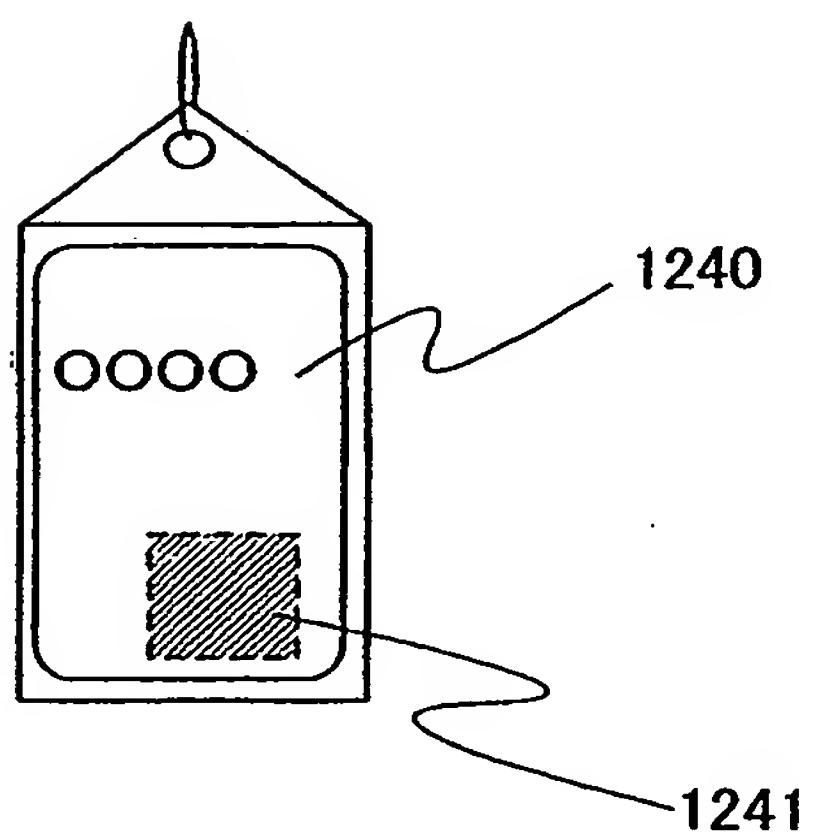
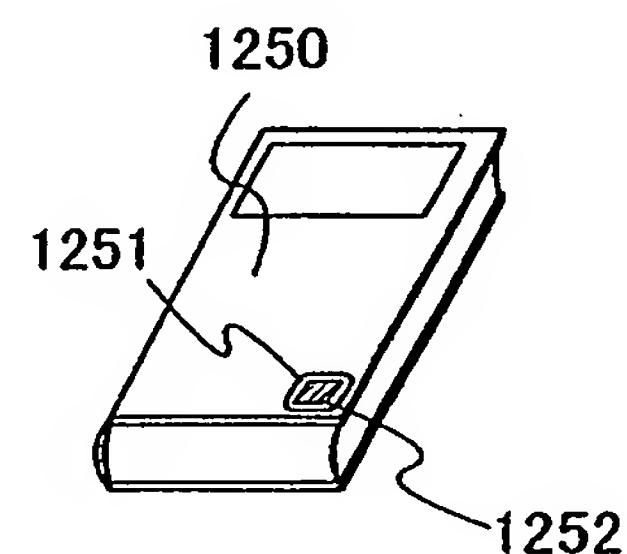
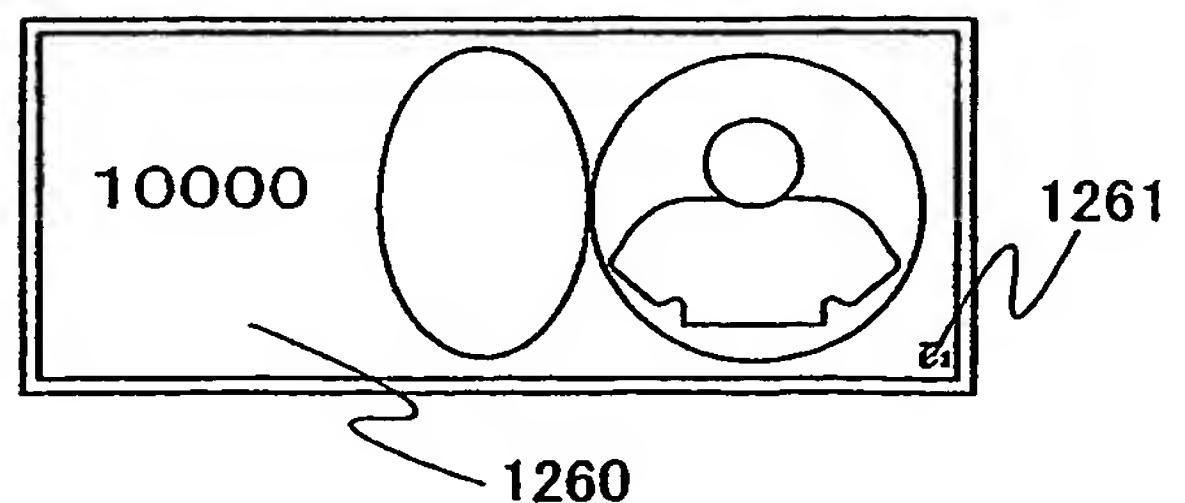
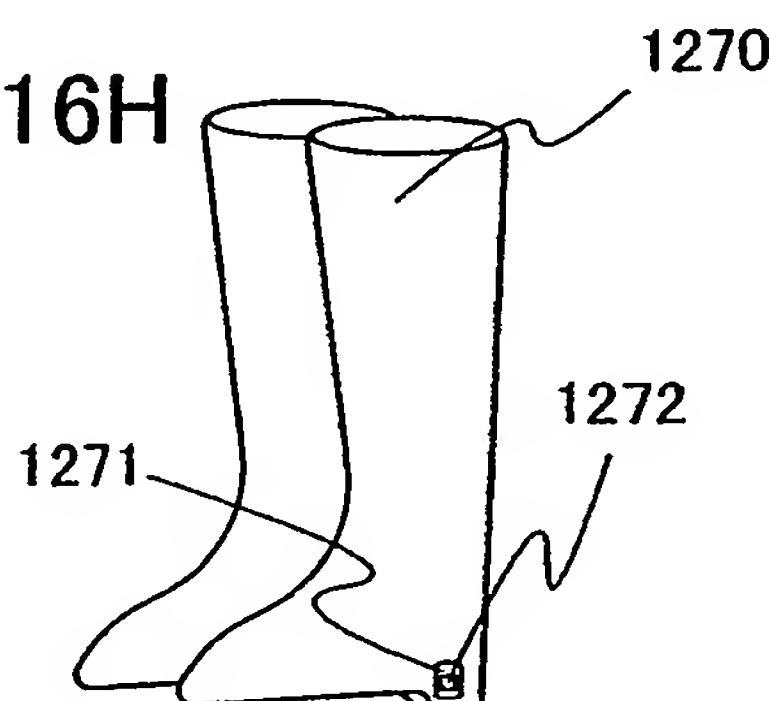
FIG. 16A**FIG. 1B****FIG. 16C****FIG. 16D****FIG. 16E****FIG. 16F****FIG. 16G****FIG. 16H**

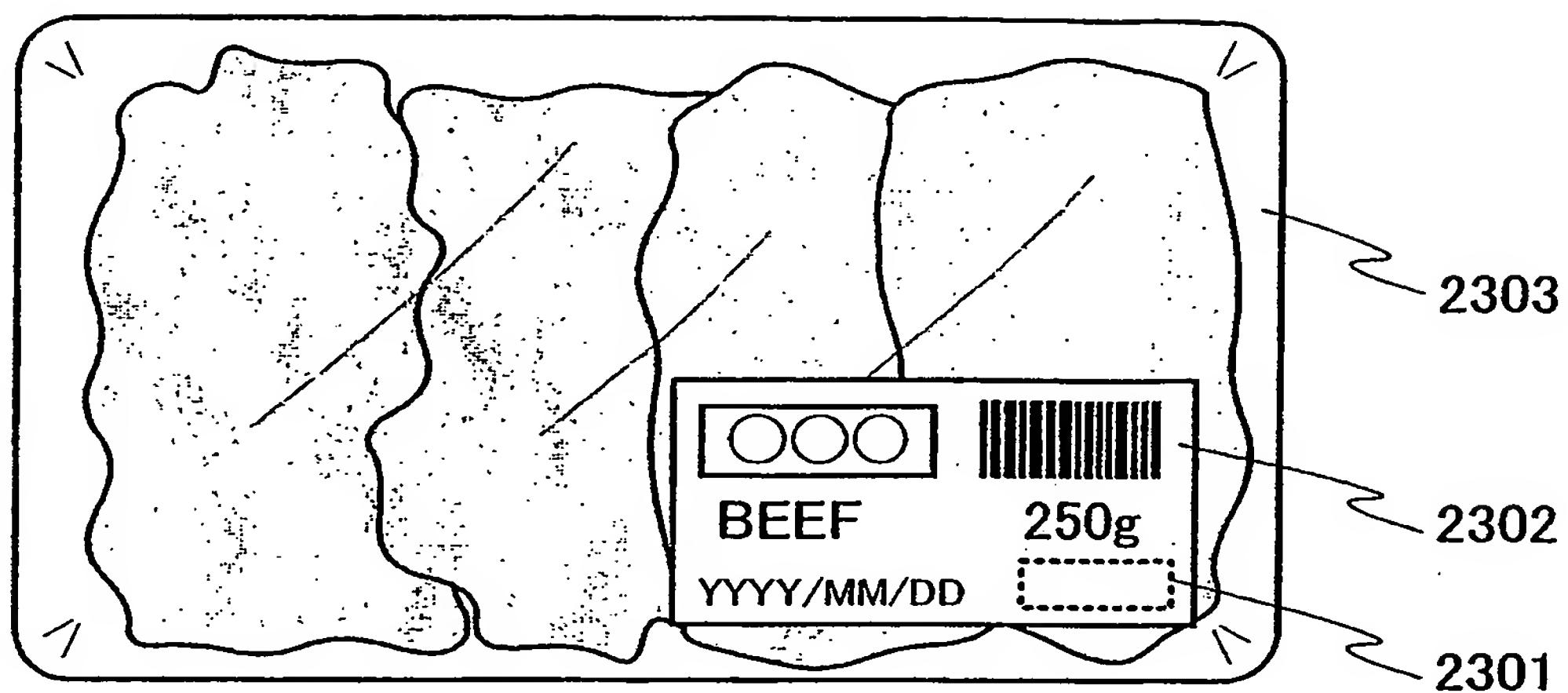
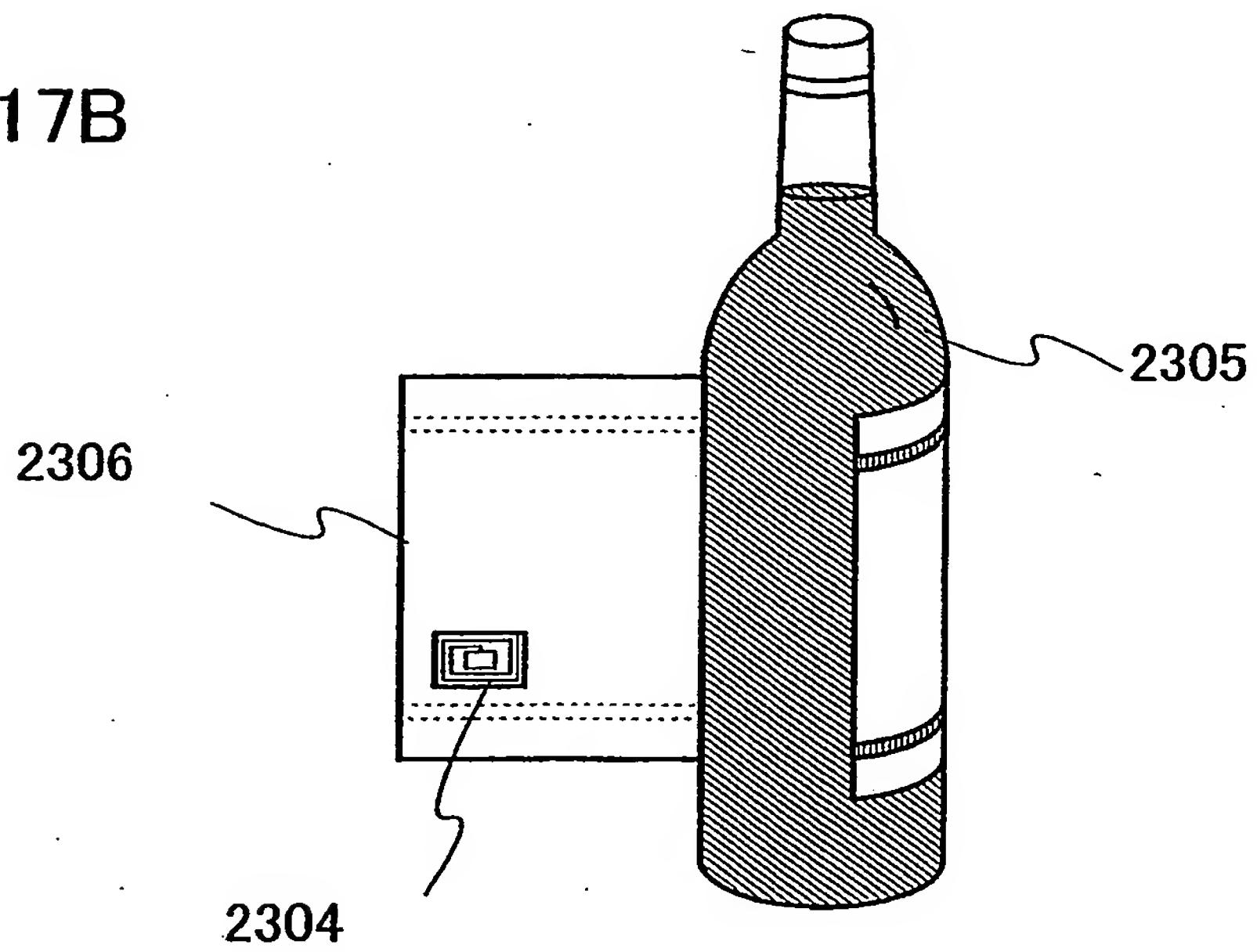
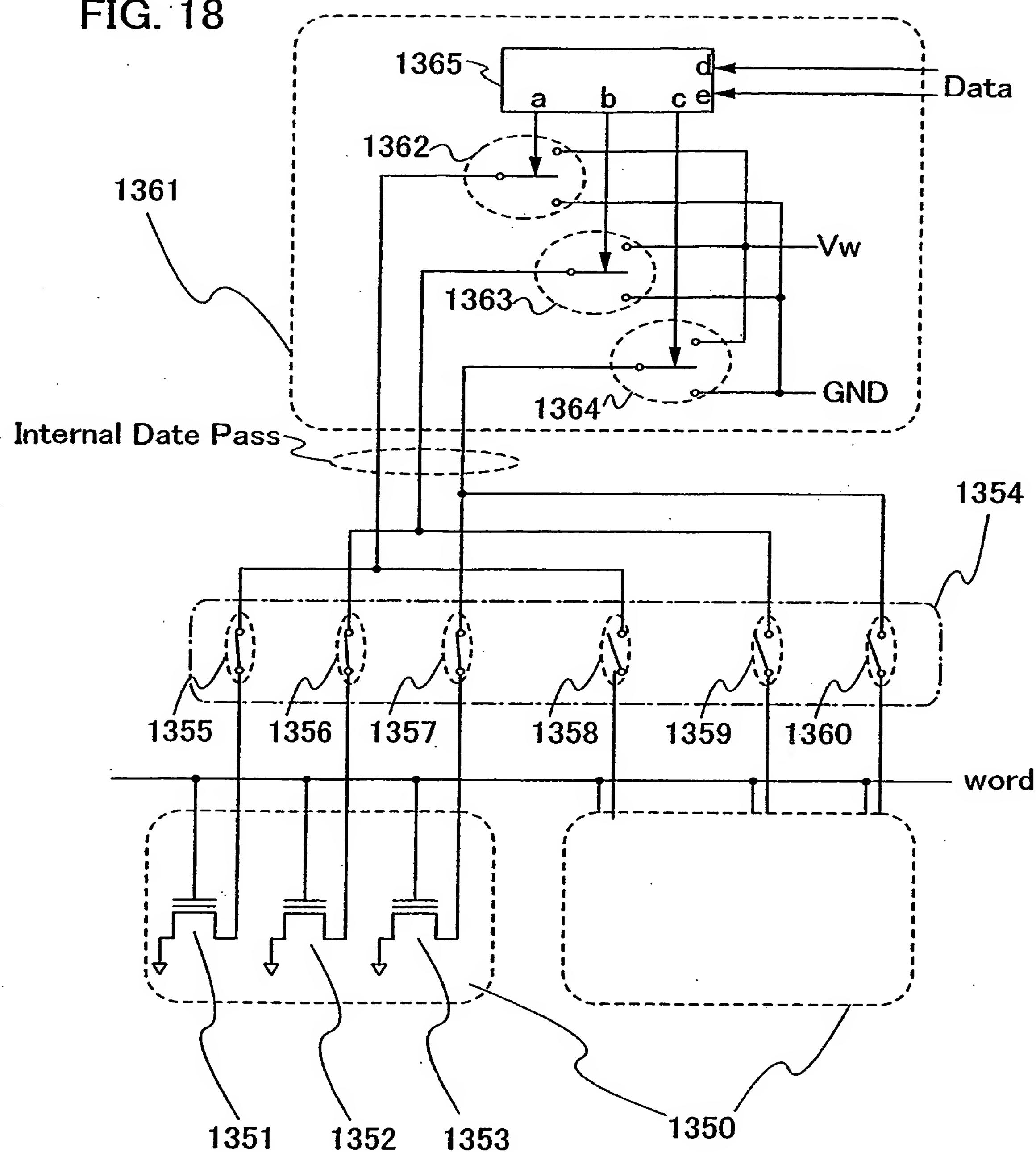
FIG. 17A**FIG. 17B**

FIG. 18



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FIG. 19

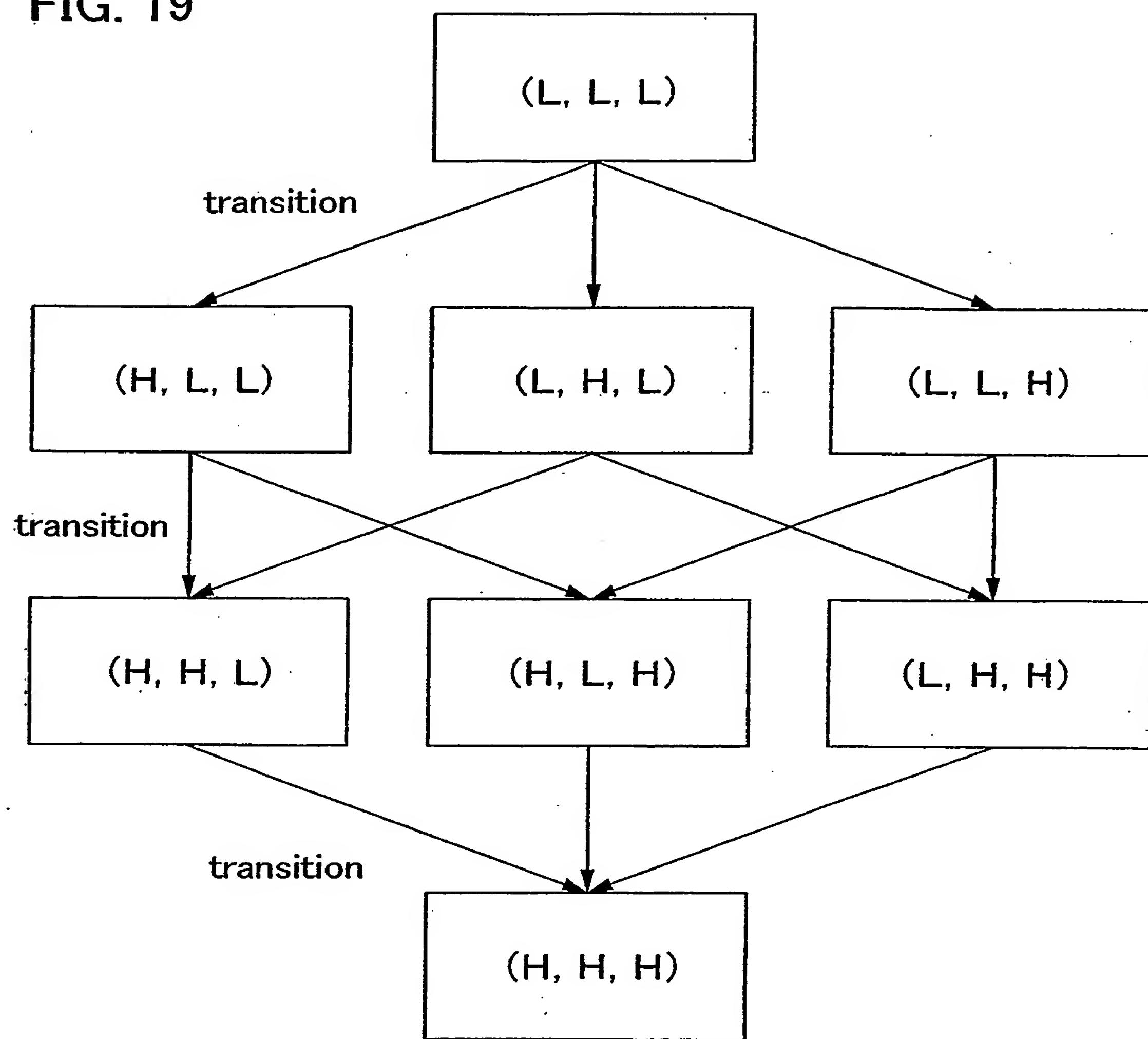


FIG. 20A

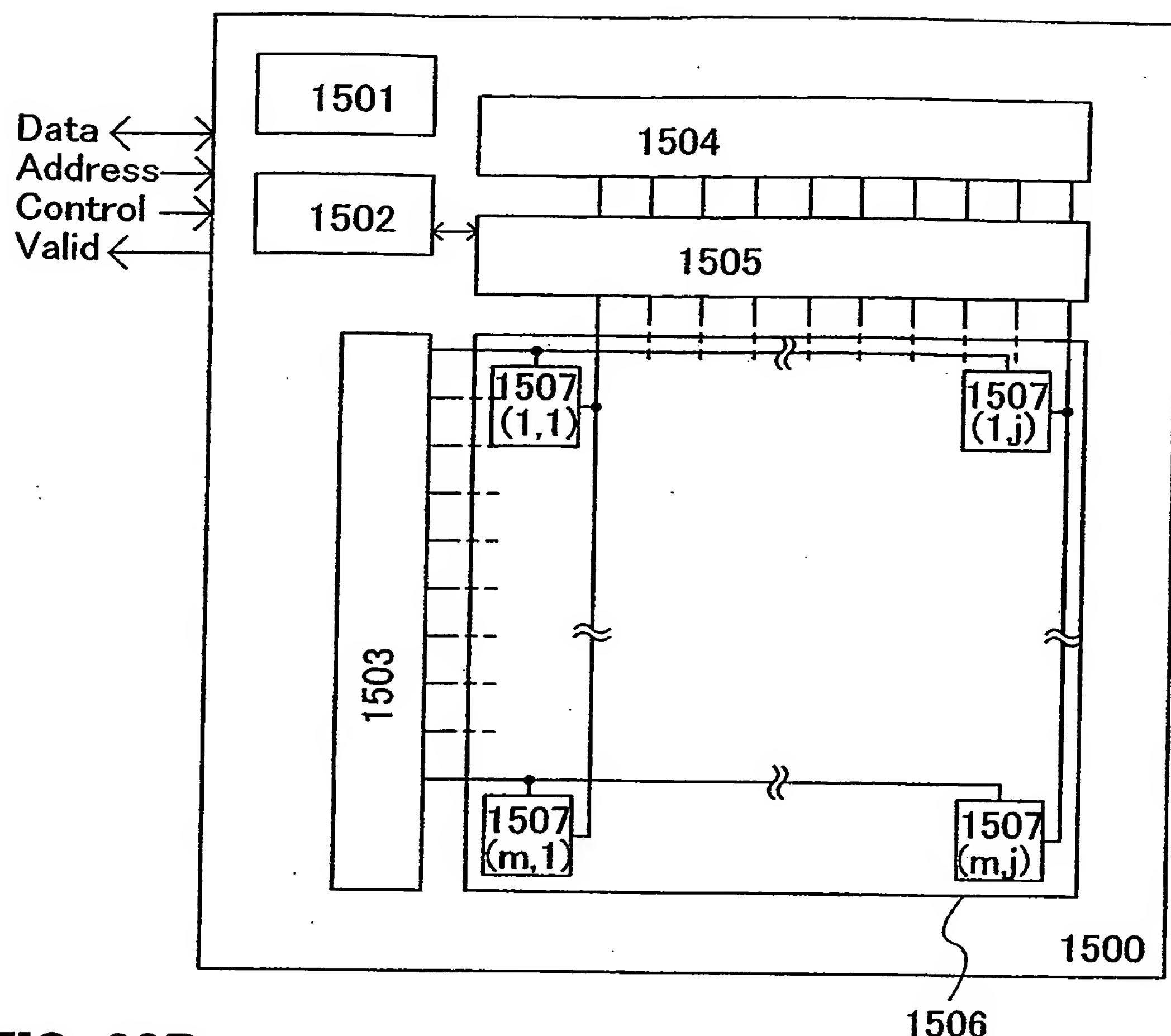


FIG. 20B

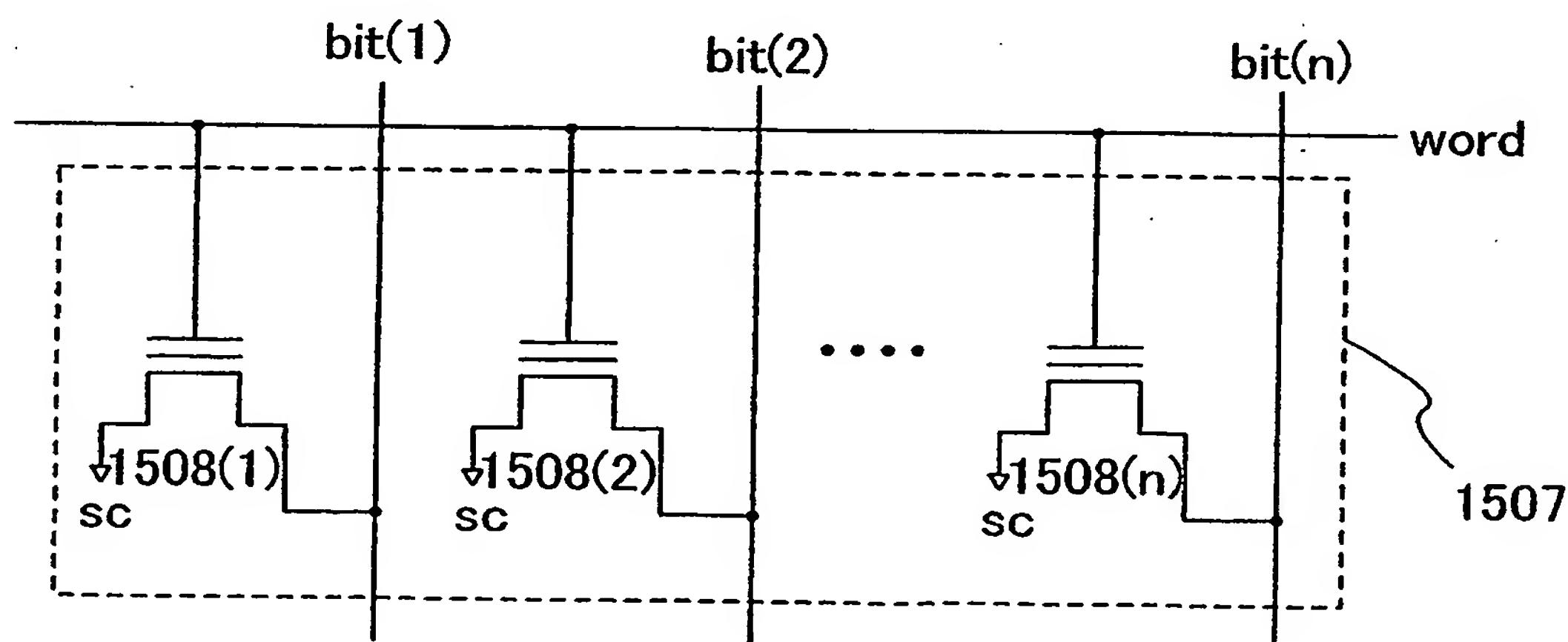


FIG. 21

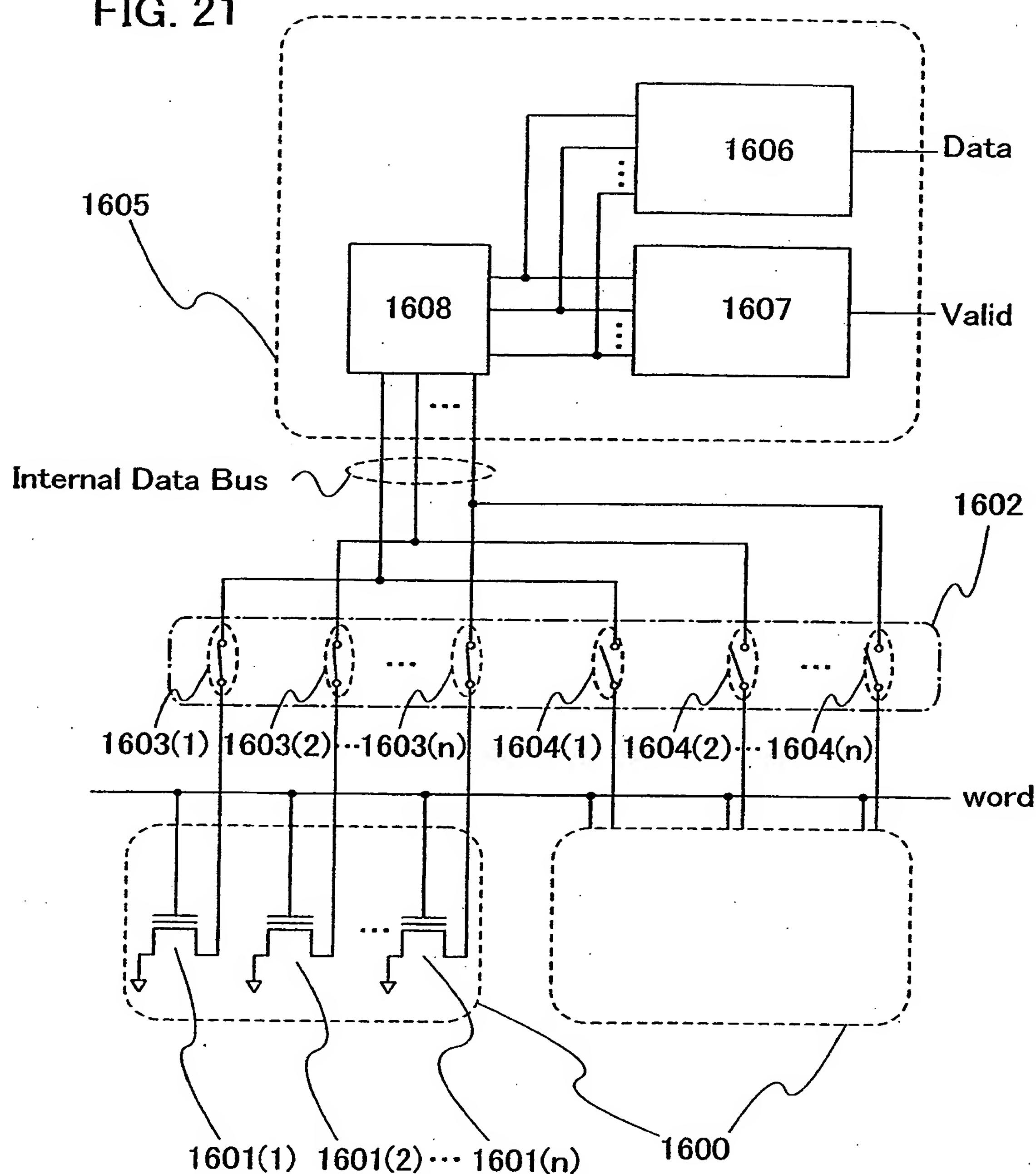


FIG. 22

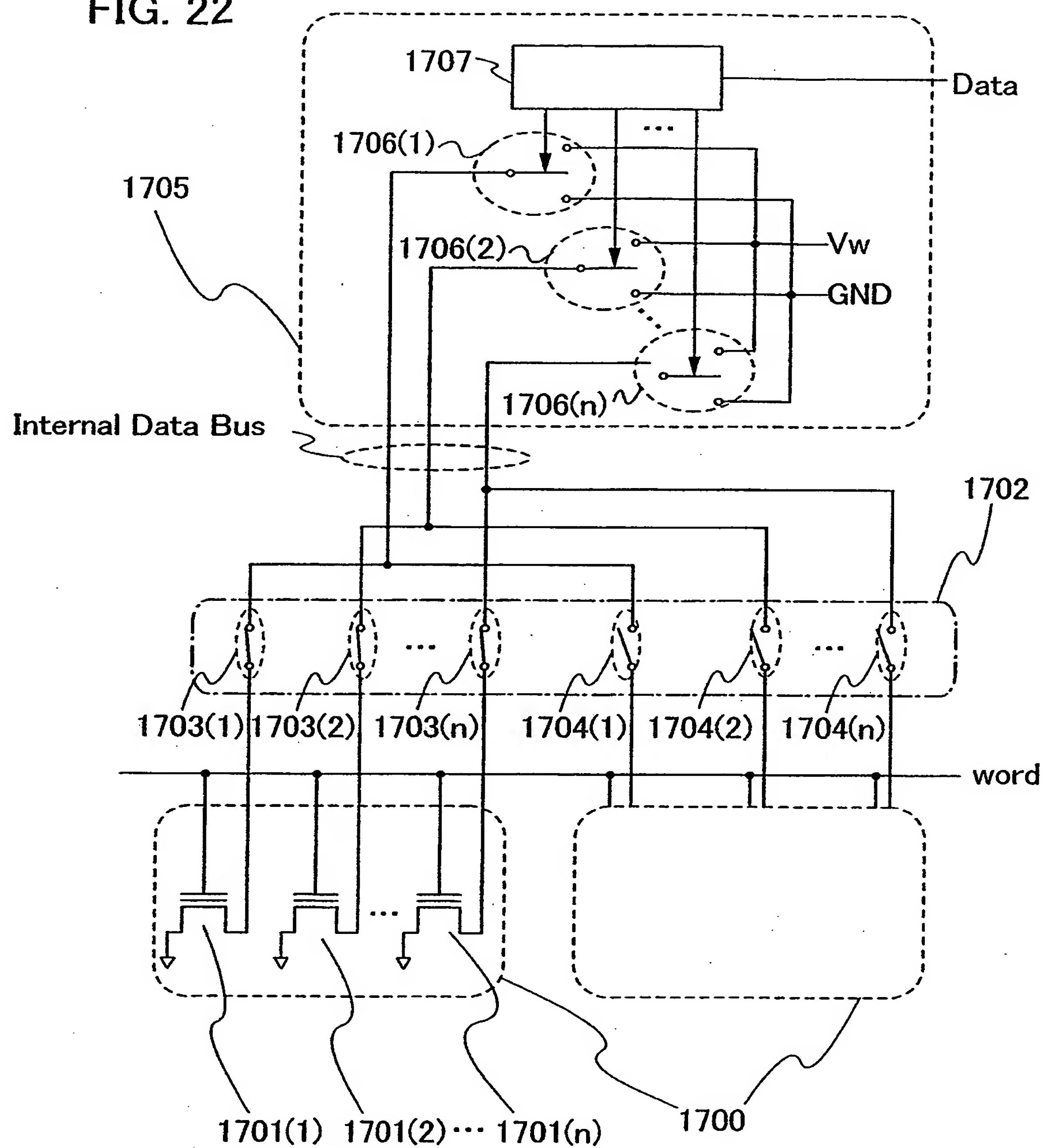
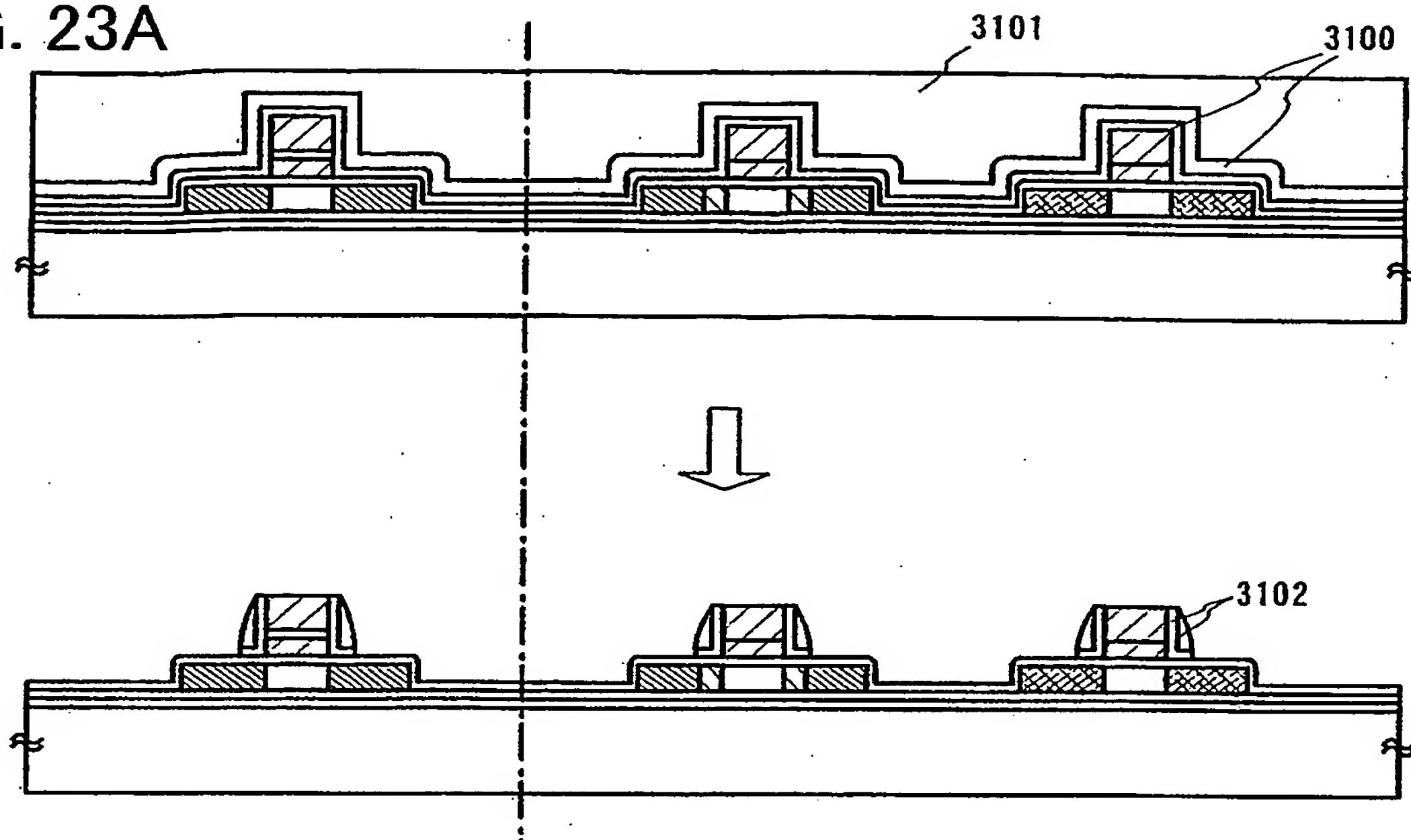
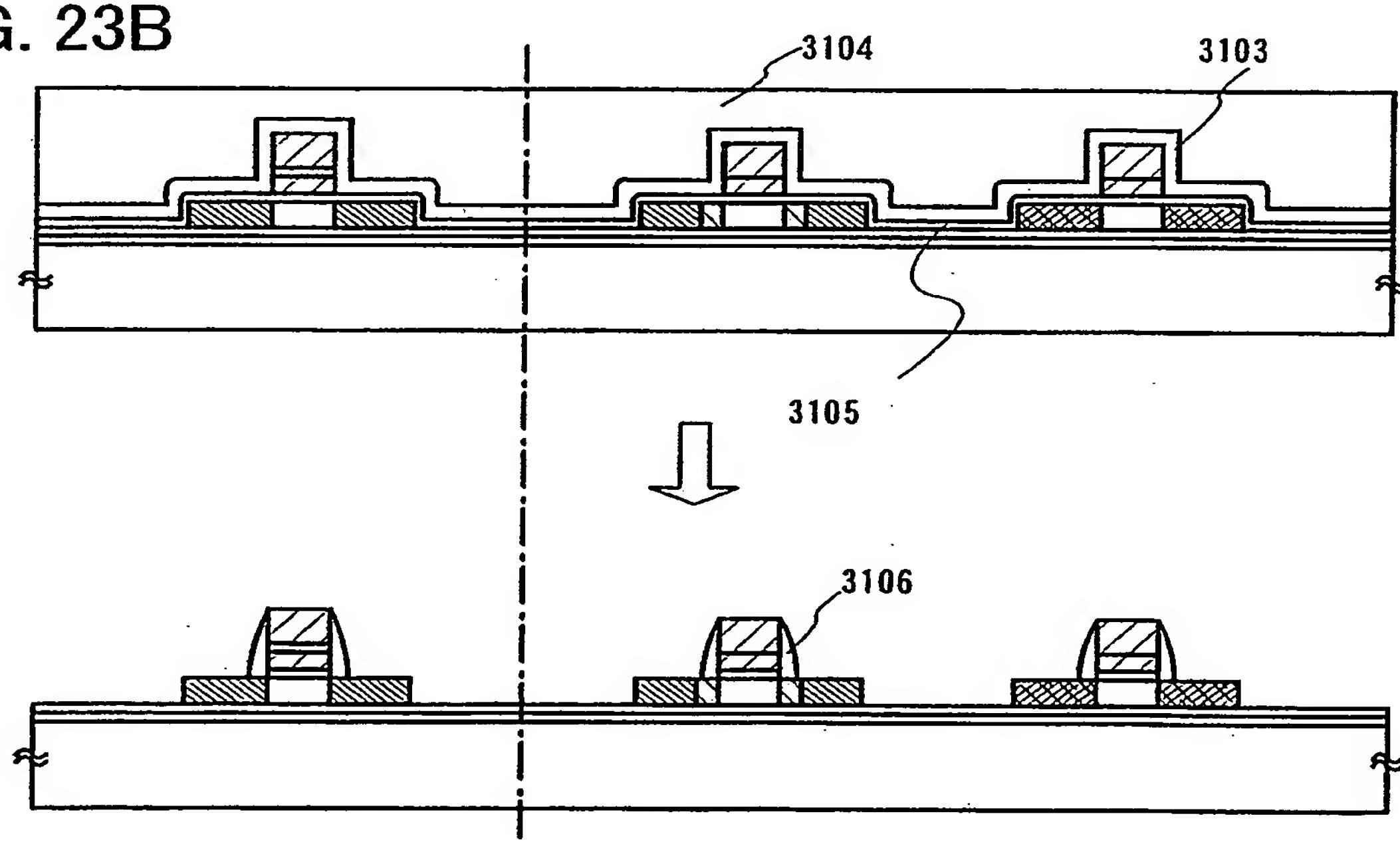


FIG. 23A**FIG. 23B**

EXPLANATION OF REFERENCE

100: substrate, 101: write circuit, 102: read circuit, 103: row decoder, 104: column decoder, 105: selector, 106: memory cell array, 107: memory cell, 108: first memory element, 109: second memory element, 150: substrate, 151: write circuit, 152: read circuit, 153: row decoder, 154: column decoder, 155: selector, 156: memory cell array, 157: memory cell, 158: first memory element, 159: second memory element, 160: third memory element, 200: memory cell, 201: first memory element, 202: second memory element, 203: selector, 204: switch, 205: switch, 206: switch, 207: switch, 208: switch, 209: switch, 210: read circuit, 211: XOR gate, 212: resistor, 213: resistor, 250: memory cell, 251: first memory element, 252: second memory element, 253: third memory element, 254: selector, 255: switch, 256: switch, 257: switch, 258: switch, 259: switch, 260: switch, 261: read circuit, 262: converting circuit, 263: determining circuit, 264: read circuit, 800: MNOS memory element, 801: gate electrode, 802: nitride film, 803: oxide film, 804: substrate, 805: source region, 806: drain region, 810: MONOS memory element, 811: gate electrode, 812: oxide film, 813: nitride film, 814: oxide film, 815: substrate, 816: source region, 817: drain region, 900: memory element, 901: gate electrode, 902: microcrystalline Si layer, 903: substrate, 904: source region, 905: drain region, 1001: IDF chip, 1002: bag, 1003: IDF chip, 1004: passport, 1005: IDF chip, 1006: driver's license, 1101: IDF chip, 1102, paper money, 1103: thin film transistor, 1104: source region, 1105: channel forming region, 1106: drain region, 1200: IC card, 1201: incorporated memory, 1210: ID tag, 1211: incorporated memory, 1220: product, 1221: protective film, 1222: ID chip, 1230: housing, 1231: ID chip, 1240: tag, 1241: ID chip, 1250: book, 1251: protective film, 1252: ID chip, 1260: paper money, 1261: ID chip, 1270: shoe, 1271: protective film, 1272: ID chip, 1300: memory cell, 1301: first memory element, 1302: second memory element, 1303: selector, 1304: switch, 1305: switch, 1306: switch, 1307: switch, 1308: switch, 1309: switch, 1310: write circuit, 1311:

switch, 1312: switch, 1313: inverter, 1350: memory cell, 1351: first memory element, 1352: second memory element, 1353: third memory element, 1354: selector, 1355: switch, 1356: switch, 1357: switch, 1358: switch, 1359: switch, 1360: switch, 1361: write circuit, 1362: switch, 1363: switch, 1364: switch, 1365: converting circuit, 1401: ID chip, 1402: antenna, 1403: RF circuit, 1404: power source/ clock signal/ reset signal generating circuit, 1405: data demodulating/modulating circuit, 1406: controlling circuit, 1407: memory, 1500: substrate, 1501: write circuit, 1502: read circuit, 1503: row decoder, 1504: column decoder, 1505: selector, 1506: memory cell array, 1507: memory cell, 1508: memory element, 1600: memory cell, 1601: memory element, 1602: selector, 1603: switch, 1604: switch, 1605: read circuit, 1606: converting circuit, 1607: determining circuit, 1608: an internal data reading circuit, 1700: memory cell, 1701: memory element, 1702: selector, 1703: switch, 1704: switch, 1705: write circuit, 1706: switch, 1707: converting circuit, 2301: IDF chip, 2302: label, 2304: IDF chip, 2305: bottle, 2306: label, 3000: insulating substrate, 3001: base film, 3002: base film, 3003: semiconductor layer, 3004: semiconductor layer, 3005: semiconductor layer, 3006: gate insulating film, 3007: conductive layer, 3008: conductive layer, 3009: conductive layer, 3010: gate insulating film, 3011: conductive layer, 3012: conductive layer, 3013: conductive layer, 3014: impurity region, 3015: impurity region, 3016: impurity region, 3017: impurity region, 3018: impurity region, 3019: impurity region, 3020: side wall, 3012: side wall, 3022: impurity region, 3023: impurity region, 3024: interlayer film, 3025: interlayer film, 3026: electrode, 3027: electrode, 3028: electrode, 3029: electrode, 3030: electrode, 3100: insulating film, 3101: resist, 3102: side wall, 3103: insulating film, 3104: resist, 3105: gate insulating film, 3106: side wall, 4000: peeling layer, 4001: interlayer insulating film, 4004: pad, 4005: pad, 4006: protective layer, 4007: groove, 4008: adhesive, 4009: support base.